

LMV321A-Q1、LMV358A-Q1、LMV324A-Q1 汽车类、低电压、轨至轨输出运算放大器

1 特性

- 符合面向汽车应用的 AEC-Q100 标准
 - 温度等级 1: -40°C 至 +125°C, TA
 - 器件 HBM ESD 分类等级 2
 - 器件 CDM ESD 分类等级 C6
- 低输入失调电压: $\pm 1\text{mV}$
- 轨至轨输出
- 单位带宽增益积: 1MHz
- 低宽带噪声: $30\text{nV}/\sqrt{\text{Hz}}$
- 低输入偏置电流: 10pA
- 低静态电流: $70\mu\text{A}/\text{通道}$
- 单位增益稳定
- 内置 RFI 和 EMI 滤波器
- 可在电源电压低至 2.5V 的情况下运行
- 由于具有电阻式开环输出阻抗, 因此可在更高的容性负载下更轻松地实现稳定
- 工作温度范围: -40°C 至 125°C

2 应用

- 针对 AEC-Q100 1 级应用进行了优化
- 信息娱乐系统与仪表组
- 被动安全
- 车身电子装置和照明
- 混合动力汽车/电动汽车逆变器和电机控制
- 车载充电器 (OBC) 和无线充电器
- 动力总成电流传感器
- 高级驾驶辅助系统 (ADAS)
- 单电源、低侧、单向电流感应电路

3 说明

LMV3xxA-Q1 系列包括单通道 (LMV321A-Q1)、双通道 (LMV358A-Q1) 和四通道 (LMV324A-Q1) 低压 (2.5V 至 5.5V) 汽车类运算放大器, 具有轨至轨输出摆幅功能。这些运算放大器为空间受限、需要低压运行和高容性负载驱动的应用 (例如信息娱乐系统和照明) 提供了一种具有成本效益的方法。LMV3xxA-Q1 系列的容性负载驱动具有 500pF 的电容, 而电阻式开环输出阻抗使其易于在更高的容性负载下保持稳定。这些运算放大器专为低工作电压 (2.5V 至 5.5V) 而设计, 性能规格类似于 LMV3xx-Q1 器件。

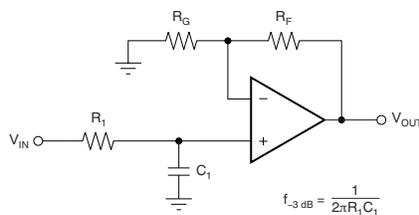
LMV3xxA-Q1 系列的稳健设计可简化电路设计。这些运算放大器具有单位增益稳定性, 集成了 RFI 和 EMI 抑制滤波器, 并且在过驱情况下不会出现相位反转。

LMV3xxA-Q1 可采用 SOIC、MSOP、SOT-23 和 TSSOP 等业界通用的封装。

封装信息⁽¹⁾

器件型号	封装	封装尺寸 (标称值)
LMV321A-Q1	DBV (SOT-23, 5)	1.60mm × 2.90mm
	DCK (SC70, 5)	1.25mm × 2.00mm
LMV358A-Q1	D (SOIC, 8)	3.91mm × 4.90mm
	DGK (VSSOP, 8)	3.00mm × 3.00mm
LMV324A-Q1	D (SOIC, 14)	8.65mm × 3.91mm
	PW (TSSOP, 14)	4.40mm × 5.00mm
	DYY (SOT-23, 14)	4.20mm × 1.90mm

(1) 如需了解所有可用封装, 请参阅数据表末尾的可订购产品附录。



$$\frac{V_{OUT}}{V_{IN}} = \left(1 + \frac{R_F}{R_G}\right) \left(\frac{1}{1 + sR_1 C_1}\right)$$

单极低通滤波器



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4 Revision History

注：以前版本的页码可能与当前版本的页码不同

Changes from Revision C (January 2023) to Revision D (April 2023)	Page
• 将 DBV 封装状态从 <i>预发布</i> 更改为 <i>正在供货</i>	1
Changes from Revision B (October 2021) to Revision C (January 2023)	Page
• 删除了 <i>器件信息</i> 表中 SC70 (5) 封装的预发布说明.....	1
• Changed the formatting of the <i>Pin Configuration and Functions</i> section.....	3
• Changed values in <i>Thermal Information: LMV321A-Q1</i> table.....	6
Changes from Revision A (April 2021) to Revision B (October 2021)	Page
• 在数据表添加了 LMV321A-Q1 GPN.....	1
• 在 <i>器件信息</i> 表中添加了 SOT-23 (5) 和 SC70 (5) 封装.....	1
• 删除了 <i>器件信息</i> 表中 SOT-23 (14) 和 TSSOP (14) 封装的预发布说明.....	1
• Added LMV321A-Q1 SOT-23 (5), SC70 (5), and LMV321AU-Q1 SOT-23 (5) Packages, to <i>Pin Configuration and Functions</i> section.....	3
• Added <i>Thermal Information: LMV321A-Q1</i> table.....	6
Changes from Revision * (June 2020) to Revision A (April 2021)	Page
• 更新了整个文档中的表格、图和交叉参考的编号格式.....	1
• 删除了 <i>器件信息</i> 表中 VSSOP (8) 封装的预览说明.....	1
• 删除了 <i>器件信息</i> 表中的 SOT-23 (8)、TSSOP (8)、SOT-23 (5) 和 SC70 (5) 封装.....	1
• Deleted TSSOP (8) Package, from <i>Pin Configuration and Functions</i> section.....	3
• Added note (4) to differential input voltage in <i>Absolute Maximum Ratings</i> table.....	5
• Added thermal information for DGK package.....	6
• Added thermal information for DYY package.....	6

5 Pin Configuration and Functions

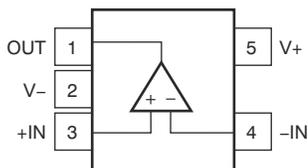


图 5-1. LMV321A-Q1 DBV Package,
5-Pin SOT-23
(Top View)

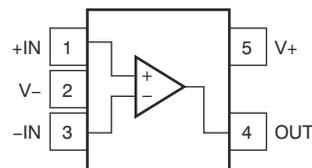


图 5-2. LMV321A-Q1 DCK, LMV321AU-Q1 DBV
Package,
5-Pin SC70, SOT-23
(Top View)

表 5-1. Pin Functions: LMV321A-Q1

NAME	PIN		TYPE (1)	DESCRIPTION
	DBV	DCK, DBV (U)		
- IN	4	3	I	Inverting input
+IN	3	1	I	Non-inverting input
OUT	1	4	O	Output
V -	2	2	—	Negative (lowest) supply or ground (for single-supply operation)
V+	5	5	—	Positive (highest) supply

(1) I = input, O = output

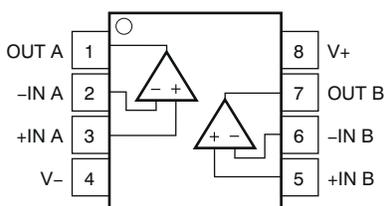
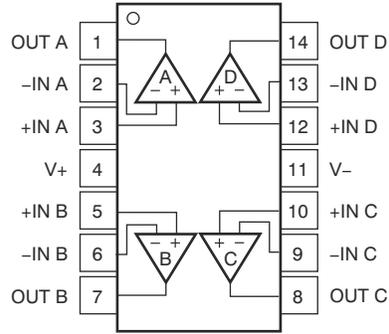


图 5-3. LMV358A-Q1 D and DGK Packages,
8-Pin SOIC and VSSOP
(Top View)

表 5-2. Pin Functions: LMV358A-Q1

NAME	PIN		TYPE ⁽¹⁾	DESCRIPTION
	NO.			
- IN A	2		I	Inverting input, channel A
+IN A	3		I	Non-inverting input, channel A
- IN B	6		I	Inverting input, channel B
+IN B	5		I	Non-inverting input, channel B
OUT A	1		O	Output, channel A
OUT B	7		O	Output, channel B
V -	4		—	Negative (lowest) supply or ground (for single-supply operation)
V+	8		—	Positive (highest) supply

(1) I = input, O = output



**图 5-4. LMV324A-Q1 D, PW, and DYY Packages,
 14-Pin SOIC, TSSOP, and SOT-23
 (Top View)**

表 5-3. Pin Functions: LMV324A-Q1

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
- IN A	2	I	Inverting input, channel A
+IN A	3	I	Non-inverting input, channel A
- IN B	6	I	Inverting input, channel B
+IN B	5	I	Non-inverting input, channel B
- IN C	9	I	Inverting input, channel C
+IN C	10	I	Non-inverting input, channel C
- IN D	13	I	Inverting input, channel D
+IN D	12	I	Non-inverting input, channel D
OUT A	1	O	Output, channel A
OUT B	7	O	Output, channel B
OUT C	8	O	Output, channel C
OUT D	14	O	Output, channel D
V -	11	—	Negative (lowest) supply or ground (for single-supply operation)
V+	4	—	Positive (highest) supply

(1) I = input, O = output

6 Specifications

6.1 Absolute Maximum Ratings

over operating temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT	
Supply voltage, ([V+] - [V-])		0	6	V	
Signal input pins	Voltage ⁽²⁾	Common-mode	(V-) - 0.5	(V+) + 0.5	V
		Differential ⁽⁴⁾	(V+) - (V-) + 0.2		V
	Current ⁽²⁾	- 10	10	mA	
Output short-circuit ⁽³⁾		Continuous			
Operating, T _A		- 55	150	°C	
Operating junction temperature, T _J			150	°C	
Storage temperature, T _{stg}		- 65	150	°C	

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5 V beyond the supply rails must be current limited to 10 mA or less.
- (3) Short-circuit to ground, one amplifier per package.
- (4) Differential input voltages greater than 0.5 V applied continuously can result in a shift to the input offset voltage and quiescent current above the maximum specifications of these parameters. The magnitude of this effect increases as the ambient operating temperature rises.

6.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2 ⁽¹⁾	±2000	V
		Charged-device model (CDM), per AEC Q100-011 CDM ESD Classification Level C5	±1000	

- (1) AEC Q100-002 indicates that HBM stressing shall be in accordance with ANSI/ESDA/JEDEC JS-001 Specification

6.3 Recommended Operating Conditions

over operating temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V _S	Supply voltage	2.5	5.5	V
T _A	Specified temperature	- 40	125	°C

6.4 Thermal Information: LMV321A-Q1

THERMAL METRIC ⁽¹⁾		LMV321A-Q1		UNIT
		DBV (SOT-23)	DCK (SC70)	
		5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	232.5	246.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	131.0	157.5	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	99.6	95.4	°C/W
ψ_{JT}	Junction-to-top characterization parameter	66.5	68.8	°C/W
ψ_{JB}	Junction-to-board characterization parameter	99.1	95.0	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#).

6.5 Thermal Information: LMV358A-Q1

THERMAL METRIC ⁽¹⁾		LMV358A-Q1		UNIT
		D (SOIC)	DGK (VSSOP)	
		8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	151.9	196.6	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	92.0	86.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	95.4	118.3	°C/W
ψ_{JT}	Junction-to-top characterization parameter	40.2	23.2	°C/W
ψ_{JB}	Junction-to-board characterization parameter	94.7	116.7	°C/W

(1) For more information about traditional and new thermal metrics, see [Semiconductor and IC Package Thermal Metrics](#).

6.6 Thermal Information: LMV324A-Q1

THERMAL METRIC ⁽¹⁾		LMV324A-Q1			UNIT
		D (SOIC)	PW (TSSOP)	DYY (SOT-23)	
		14 PINS	14 PINS	14 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	115.1	135.3	154.3	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	71.2	63.5	86.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	71.1	78.4	67.9	°C/W
ψ_{JT}	Junction-to-top characterization parameter	29.6	13.6	10.1	°C/W
ψ_{JB}	Junction-to-board characterization parameter	70.7	77.9	67.5	°C/W

6.7 Electrical Characteristics

For $V_S = (V+) - (V-) = 2.5\text{ V to }5.5\text{ V}$ ($\pm 0.9\text{ V to } \pm 2.75\text{ V}$), $T_A = 25^\circ\text{C}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, and $V_{CM} = V_{OUT} = V_S / 2$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
V_{OS}	Input offset voltage	$V_S = 5\text{ V}$		± 1	± 4	mV
		$V_S = 5\text{ V}$, $T_A = -40^\circ\text{C to }125^\circ\text{C}$			± 5	
dV_{OS}/dT	V_{OS} vs temperature	$T_A = -40^\circ\text{C to }125^\circ\text{C}$		± 1		$\mu\text{V}/^\circ\text{C}$
PSRR	Power-supply rejection ratio	$V_S = 2.5\text{ to }5.5\text{ V}$, $V_{CM} = (V-)$	78	100		dB
INPUT VOLTAGE RANGE						
V_{CM}	Common-mode voltage range	No phase reversal, rail-to-rail input	$(V-) - 0.1$		$(V+) - 1$	V
CMRR	Common-mode rejection ratio	$V_S = 2.5\text{ V}$, $(V-) - 0.1\text{ V} < V_{CM} < (V+) - 1.4\text{ V}$ $T_A = -40^\circ\text{C to }125^\circ\text{C}$		86		dB
		$V_S = 5.5\text{ V}$, $(V-) - 0.1\text{ V} < V_{CM} < (V+) - 1.4\text{ V}$ $T_A = -40^\circ\text{C to }125^\circ\text{C}$		95		
		$V_S = 5.5\text{ V}$, $(V-) - 0.1\text{ V} < V_{CM} < (V+) + 0.1\text{ V}$ $T_A = -40^\circ\text{C to }125^\circ\text{C}$	63	77		
		$V_S = 2.5\text{ V}$, $(V-) - 0.1\text{ V} < V_{CM} < (V+) + 0.1\text{ V}$ $T_A = -40^\circ\text{C to }125^\circ\text{C}$		68		
INPUT BIAS CURRENT						
I_B	Input bias current	$V_S = 5\text{ V}$		± 10		pA
I_{OS}	Input offset current			± 3		pA
NOISE						
E_n	Input voltage noise (peak-to-peak)	$f = 0.1\text{ Hz to }10\text{ Hz}$, $V_S = 5\text{ V}$		5.1		μV_{PP}
e_n	Input voltage noise density	$f = 1\text{ kHz}$, $V_S = 5\text{ V}$		33		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 10\text{ kHz}$, $V_S = 5\text{ V}$		30		
i_n	Input current noise density	$f = 1\text{ kHz}$, $V_S = 5\text{ V}$		25		$\text{fA}/\sqrt{\text{Hz}}$
INPUT CAPACITANCE						
C_{ID}	Differential			1.5		pF
C_{IC}	Common-mode			5		pF
OPEN-LOOP GAIN						
A_{OL}	Open-loop voltage gain	$V_S = 5.5\text{ V}$, $(V-) + 0.05\text{ V} < V_O < (V+) - 0.05\text{ V}$, $R_L = 10\text{ k}\Omega$	100	115		dB
		$V_S = 2.5\text{ V}$, $(V-) + 0.04\text{ V} < V_O < (V+) - 0.04\text{ V}$, $R_L = 10\text{ k}\Omega$		98		
		$V_S = 2.5\text{ V}$, $(V-) + 0.1\text{ V} < V_O < (V+) - 0.1\text{ V}$, $R_L = 2\text{ k}\Omega$		112		
		$V_S = 5.5\text{ V}$, $(V-) + 0.15\text{ V} < V_O < (V+) - 0.15\text{ V}$, $R_L = 2\text{ k}\Omega$		128		
FREQUENCY RESPONSE						
GBW	Gain-bandwidth product	$V_S = 5\text{ V}$		1		MHz
ϕ_m	Phase margin	$V_S = 5.5\text{ V}$, $G = 1$		76		$^\circ$
SR	Slew rate	$V_S = 5\text{ V}$		1.7		V/ μs
t_s	Settling time	To 0.1%, $V_S = 5\text{ V}$, 2-V step, $G = +1$, $C_L = 100\text{ pF}$		3		μs
		To 0.01%, $V_S = 5\text{ V}$, 2-V step, $G = +1$, $C_L = 100\text{ pF}$		4		
t_{OR}	Overload recovery time	$V_S = 5\text{ V}$, $V_{IN} \times \text{gain} > V_S$		0.9		μs
THD+N	Total harmonic distortion + noise	$V_S = 5.5\text{ V}$, $V_{CM} = 2.5\text{ V}$, $V_O = 1\text{ V}_{RMS}$, $G = +1$, $f = 1\text{ kHz}$, 80-kHz measurement BW		0.005%		
OUTPUT						
V_O	Voltage output swing from supply rails	$V_S = 5.5\text{ V}$, $R_L = 10\text{ k}\Omega$		20	50	mV
		$V_S = 5.5\text{ V}$, $R_L = 2\text{ k}\Omega$		40	75	
I_{SC}	Short-circuit current	$V_S = 5.5\text{ V}$		± 40		mA
Z_O	Open-loop output impedance	$V_S = 5\text{ V}$, $f = 1\text{ MHz}$		1200		Ω
POWER SUPPLY						
V_S	Specified voltage range		2.5 (± 1.25)		5.5 (± 2.75)	V
I_Q	Quiescent current per amplifier	$I_O = 0\text{ mA}$, $V_S = 5.5\text{ V}$		70	125	μA
		$I_O = 0\text{ mA}$, $V_S = 5.5\text{ V}$, $T_A = -40^\circ\text{C to }125^\circ\text{C}$			150	
	Power-on time	$V_S = 0\text{ V to }5\text{ V}$, to 90% I_Q level		50		μs

6.8 Typical Characteristics

at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)

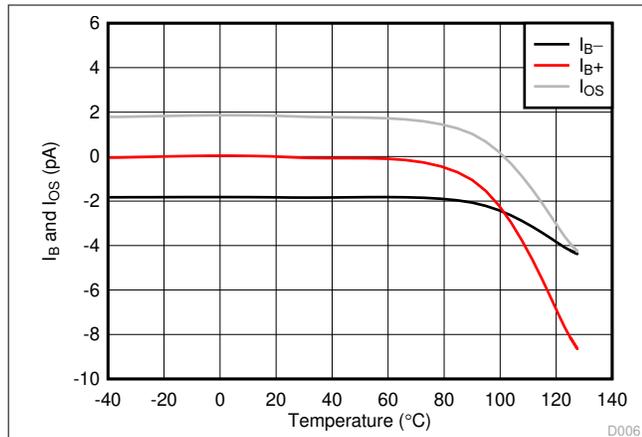


图 6-1. I_B and I_{OS} vs Temperature

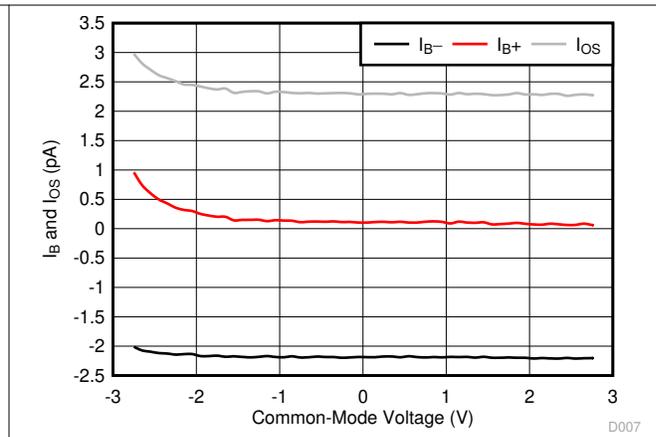


图 6-2. I_B and I_{OS} vs Common-Mode Voltage

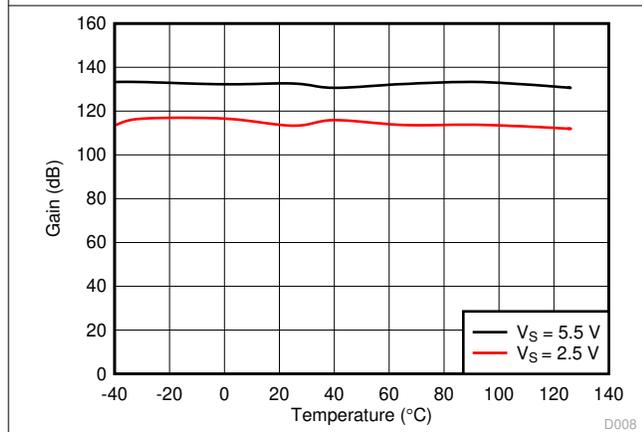


图 6-3. Open-Loop Gain vs Temperature

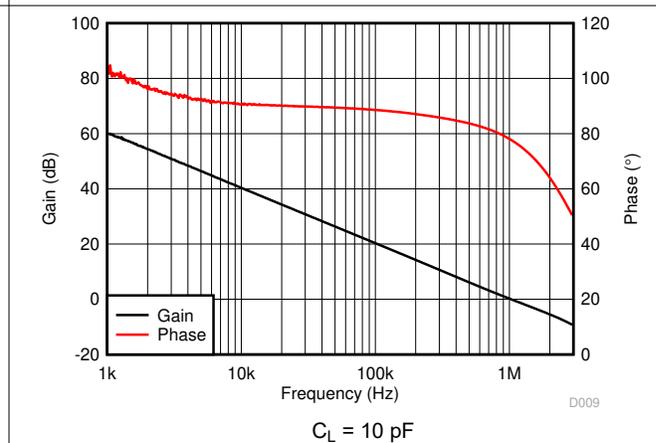


图 6-4. Open-Loop Gain and Phase vs Frequency

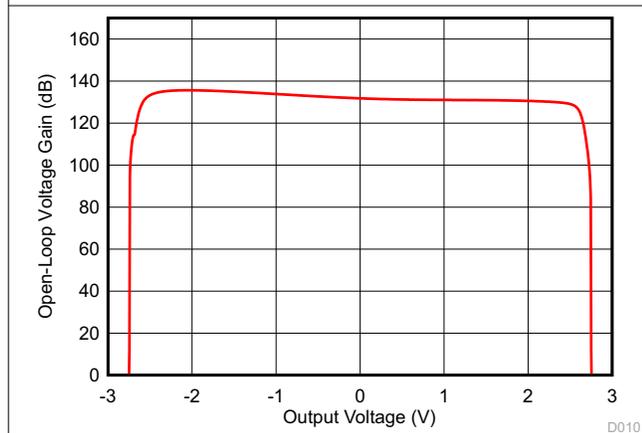


图 6-5. Open-Loop Gain vs Output Voltage

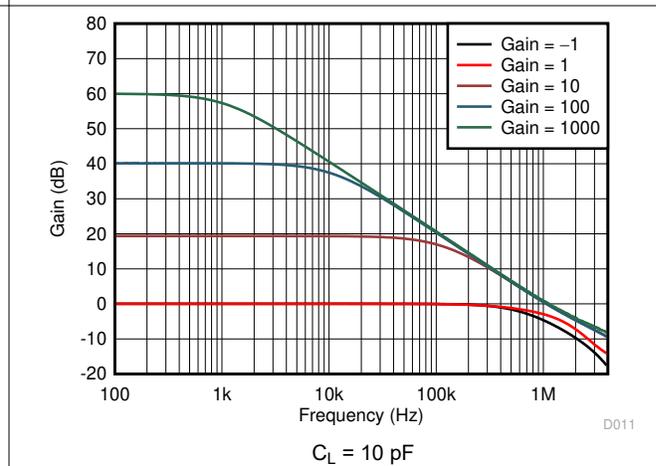


图 6-6. Closed-Loop Gain vs Frequency

6.8 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)

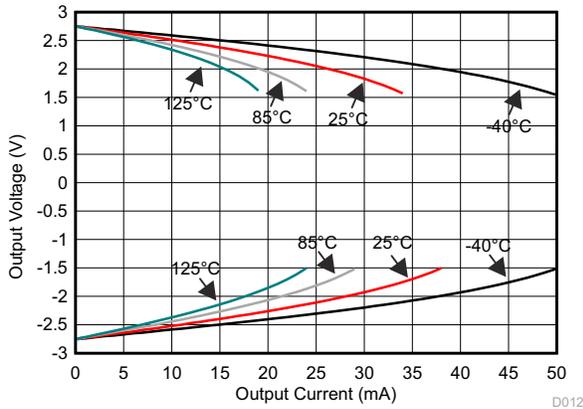


图 6-7. Output Voltage vs Output Current (Claw)

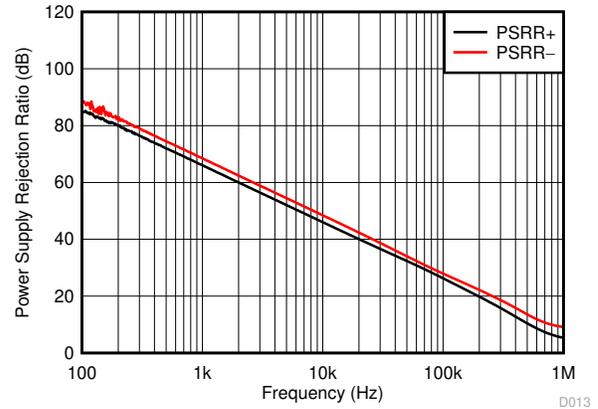


图 6-8. PSRR vs Frequency

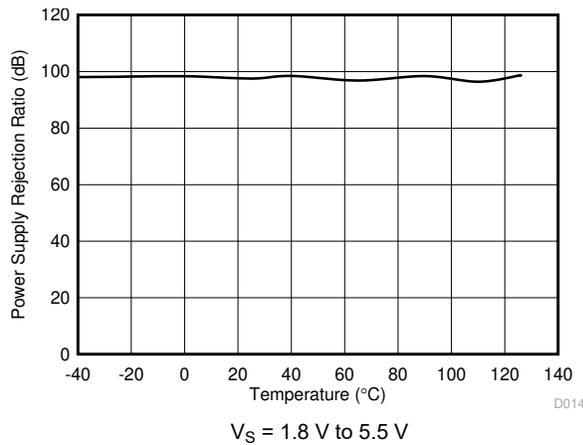


图 6-9. DC PSRR vs Temperature

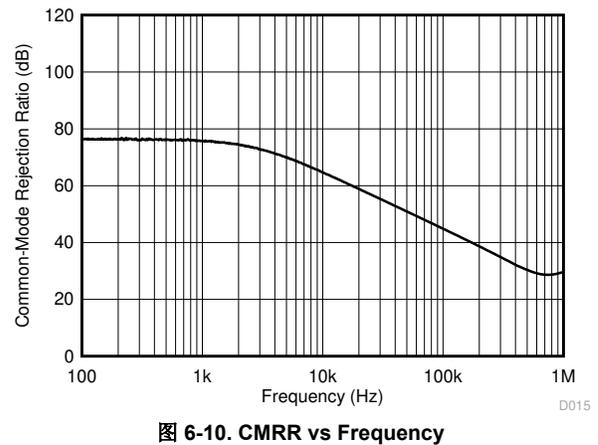


图 6-10. CMRR vs Frequency

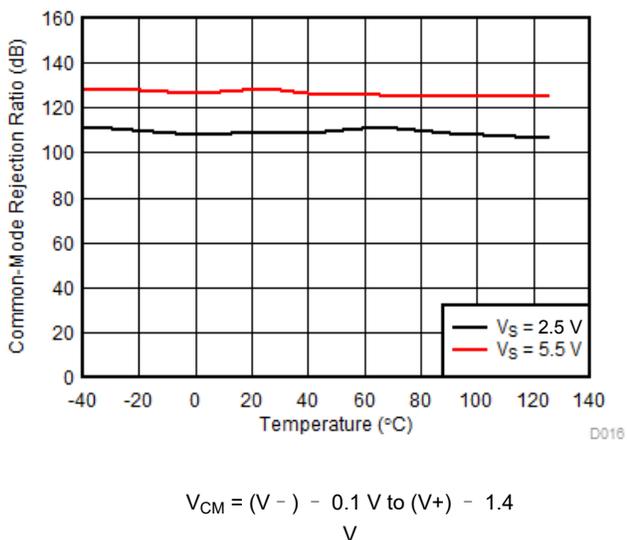


图 6-11. DC CMRR vs Temperature

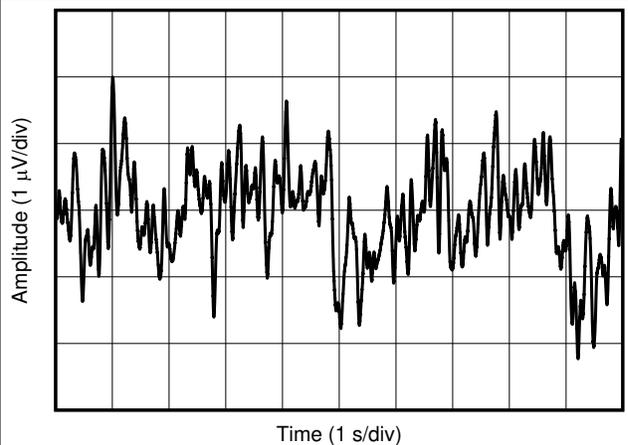


图 6-12. 0.1 Hz to 10 Hz Integrated Voltage Noise

6.8 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)

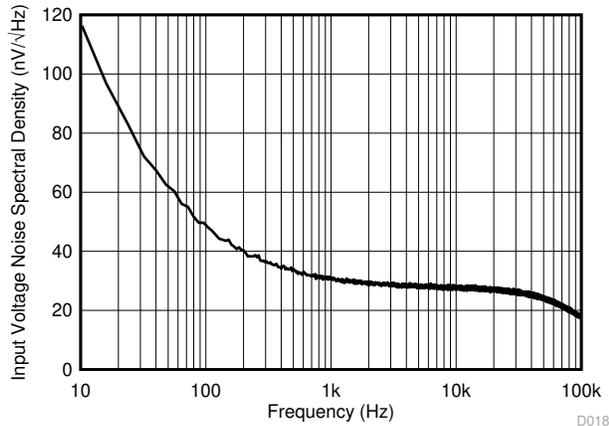


图 6-13. Input Voltage Noise Spectral Density

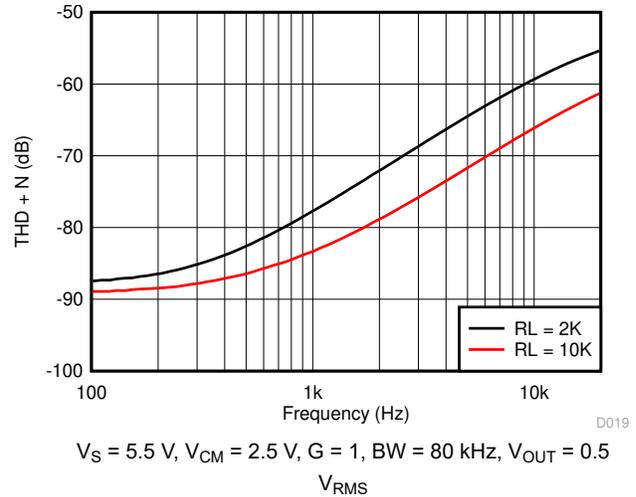


图 6-14. THD + N vs Frequency

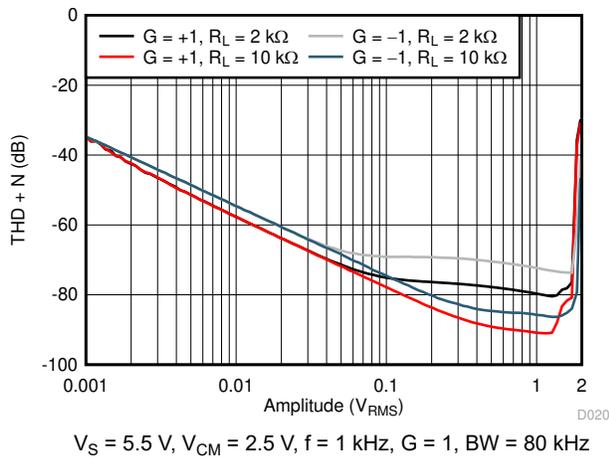


图 6-15. THD + N vs Amplitude

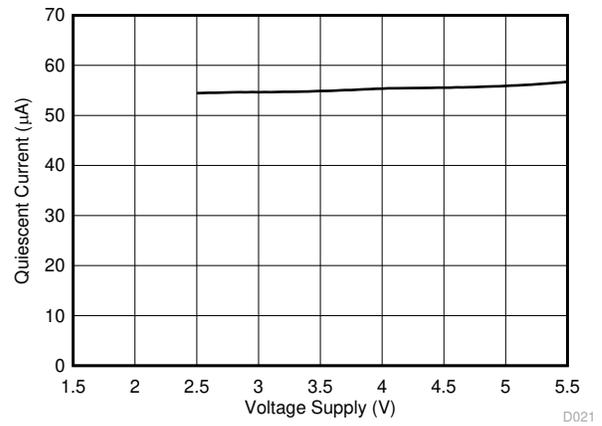


图 6-16. Quiescent Current vs Supply Voltage

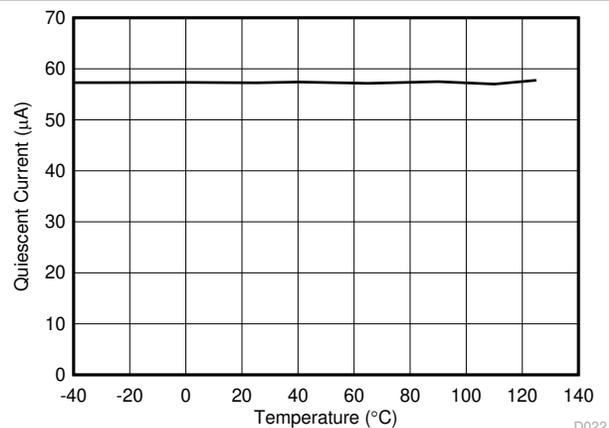


图 6-17. Quiescent Current vs Temperature

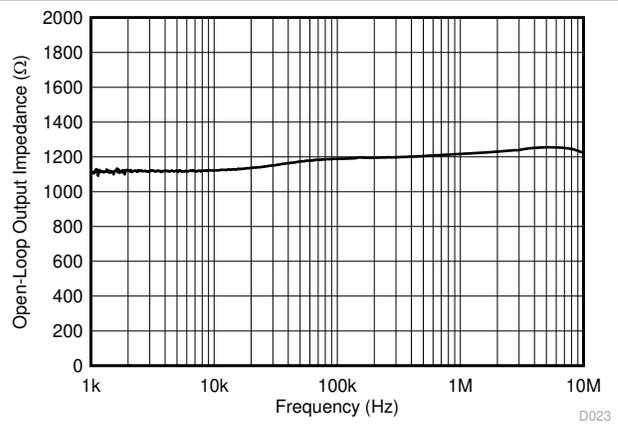


图 6-18. Open-Loop Output Impedance vs Frequency

6.8 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)

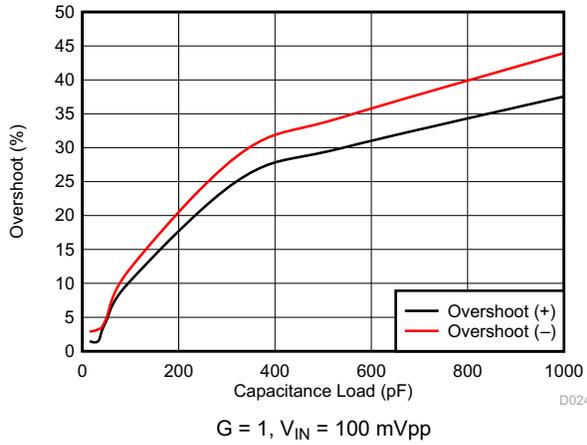


图 6-19. Small Signal Overshoot vs Capacitive Load

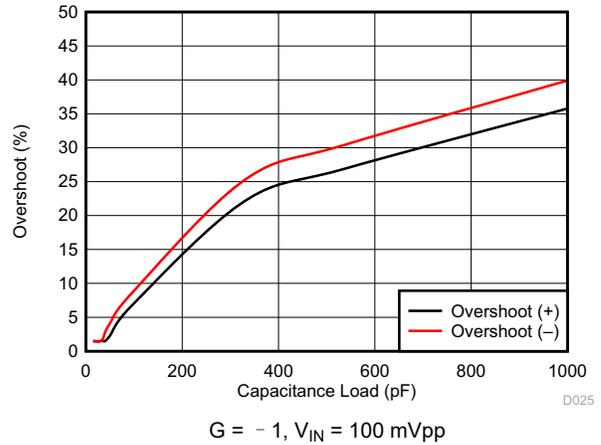


图 6-20. Small Signal Overshoot vs Capacitive Load

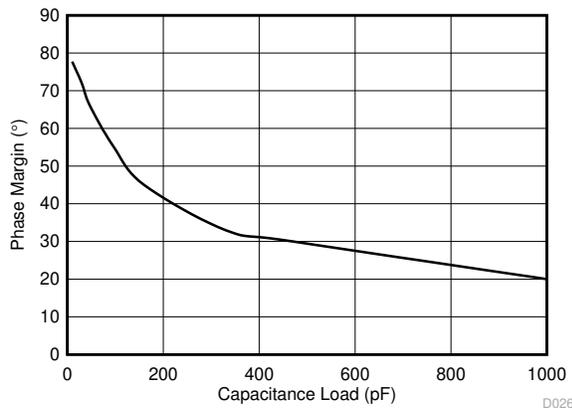


图 6-21. Phase Margin vs Capacitive Load

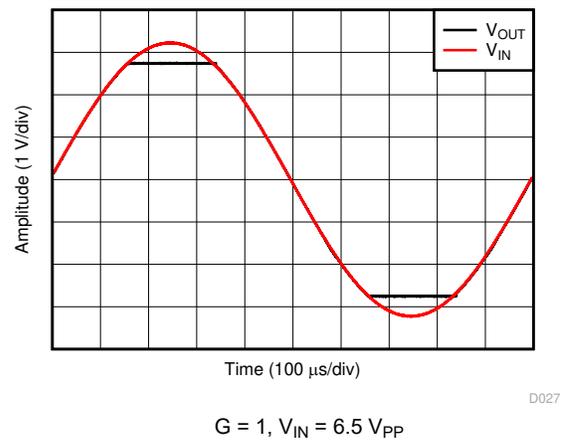


图 6-22. No Phase Reversal

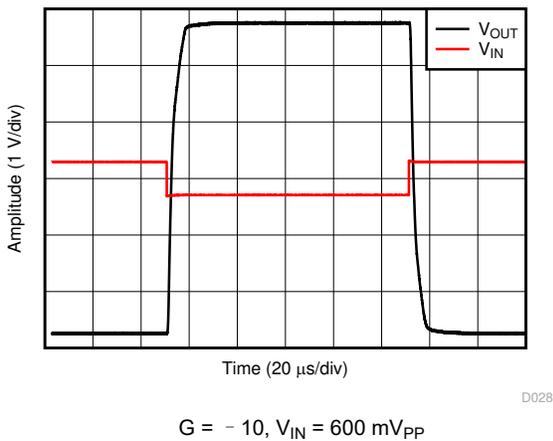


图 6-23. Overload Recovery

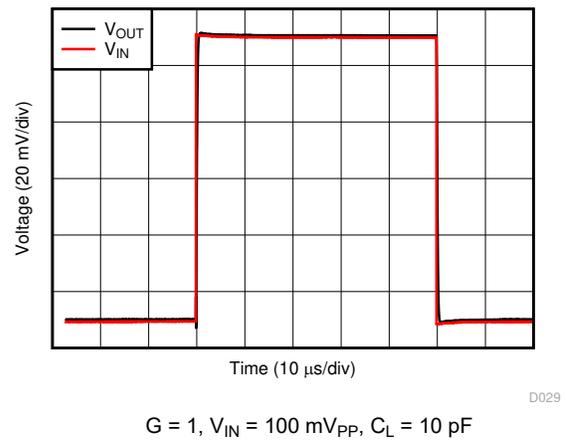
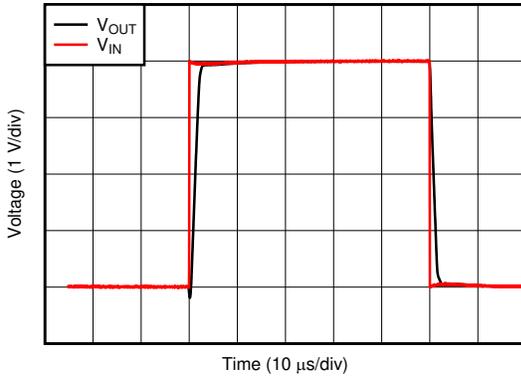


图 6-24. Small-Signal Step Response

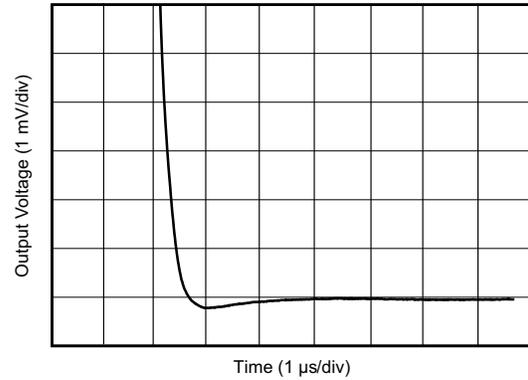
6.8 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)



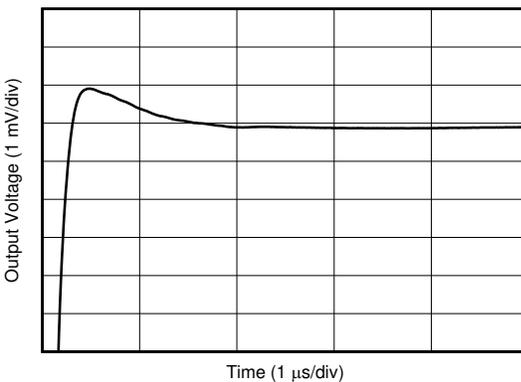
$G = 1$, $V_{IN} = 4\text{ V}_{PP}$, $C_L = 10\text{ pF}$

图 6-25. Large-Signal Step Response



$G = 1$, $C_L = 100\text{ pF}$, 2-V step

图 6-26. Large-Signal Settling Time (Negative)



$G = 1$, $C_L = 100\text{ pF}$, 2-V step

图 6-27. Large-Signal Settling Time (Positive)

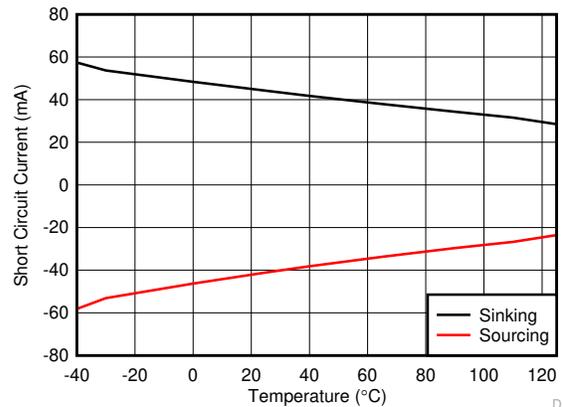


图 6-28. Short-Circuit Current vs Temperature

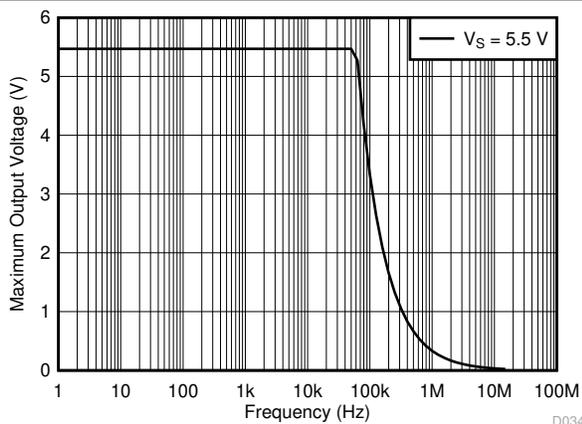


图 6-29. Maximum Output Voltage vs Frequency

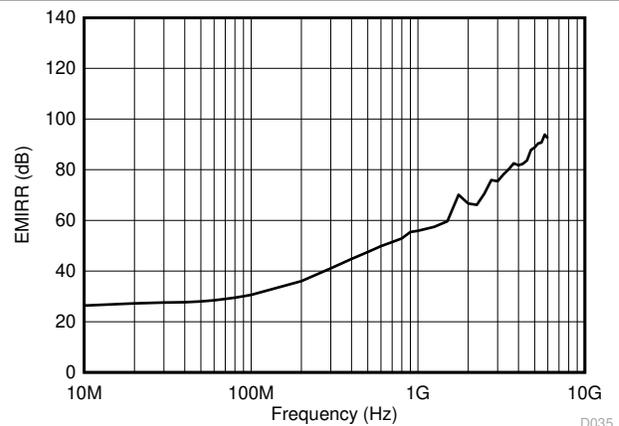


图 6-30. Electromagnetic Interference Rejection Ratio Referred to Non-inverting Input (EMIRR+) vs Frequency

6.8 Typical Characteristics (continued)

at $T_A = 25^\circ\text{C}$, $V_+ = 2.75\text{ V}$, $V_- = -2.75\text{ V}$, $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$, $V_{CM} = V_S / 2$, and $V_{OUT} = V_S / 2$ (unless otherwise noted)

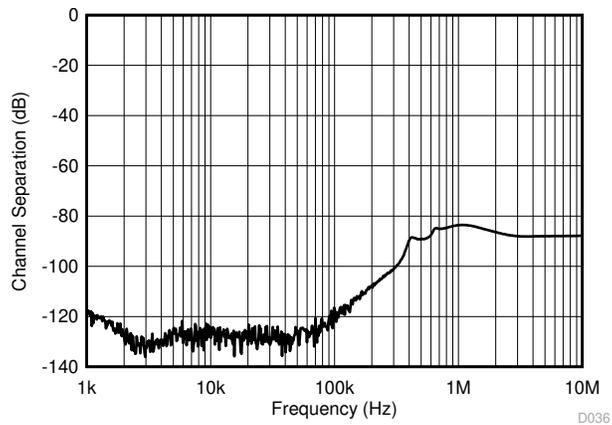


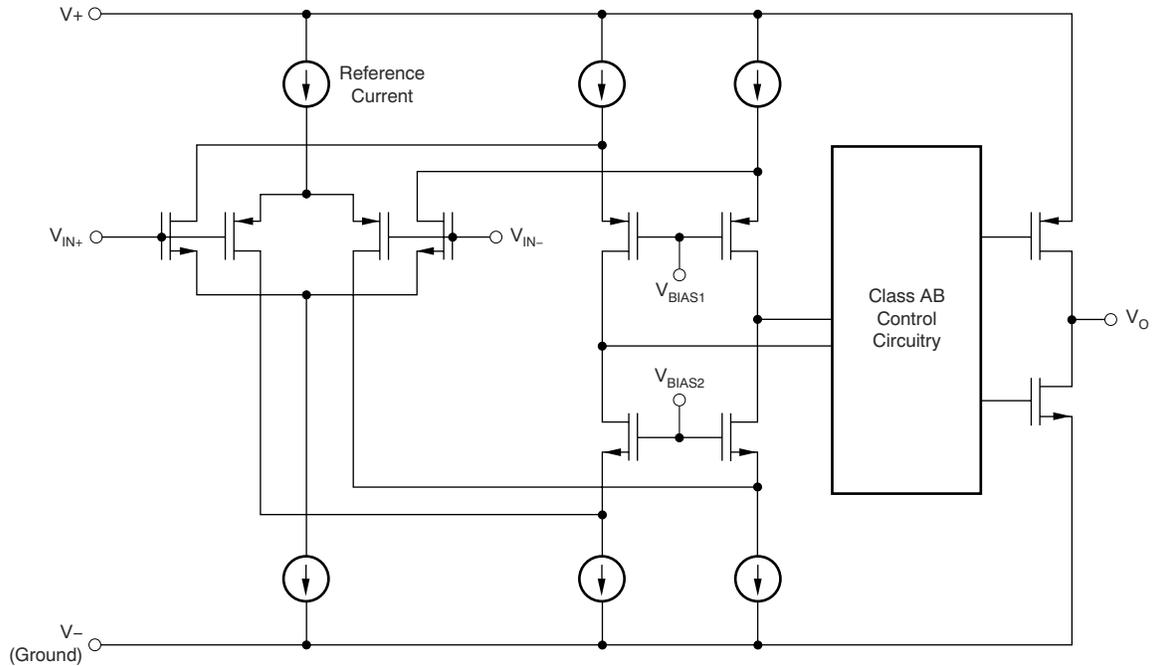
图 6-31. Channel Separation

7 Detailed Description

7.1 Overview

The LMV3xxA-Q1 is a family of low-power, rail-to-rail output op amps. These devices operate from 2.5 V to 5.5 V, are unity-gain stable, and are designed for a wide range of general-purpose applications. The input common-mode voltage range includes the negative rail and allows the LMV3xxA-Q1 family to be used in many single-supply applications. Rail-to-rail output swing significantly increases dynamic range, especially in low-supply applications, and makes the family of devices an excellent choice for driving sampling analog-to-digital converters (ADCs).

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Operating Voltage

The LMV3xxA-Q1 family of op amps are for operation from 2.5 V to 5.5 V. In addition, many specifications such as input offset voltage, quiescent current, offset current, and short circuit current apply from -40°C to 125°C . Parameters that vary significantly with operating voltages or temperature are shown in the [Typical Characteristics](#) section.

7.3.2 Input Common Mode Range

The input common-mode voltage range of the LMV3xxA-Q1 family extends 100 mV beyond the negative supply rail and within 1 V below the positive rail for the full supply voltage range of 2.5 V to 5.5 V. This performance is achieved with a P-channel differential pair, as shown in the [Functional Block Diagram](#). Additionally, a complementary N-channel differential pair has been included in parallel to eliminate issues with phase reversal that are common with previous generations of op amps. However, the N-channel pair is not optimized for operation. TI recommends limiting any voltages applied at the inputs to less than $V_{\text{CC}} - 1\text{ V}$ to make sure that the op amp conforms to the specifications detailed in the [Electrical Characteristics](#) table.

7.3.3 Rail-to-Rail Output

Designed as a low-power, low-voltage operational amplifier, the LMV3xxA-Q1 family delivers a robust output drive capability. A class-AB output stage with common-source transistors achieves full rail-to-rail output swing capability. For resistive loads of $10\text{ k}\Omega$, the output swings to within 20 mV of either supply rail, regardless of the applied power-supply voltage. Different load conditions change the ability of the amplifier to swing close to the rails.

7.3.4 Overload Recovery

Overload recovery is defined as the time required for the operational amplifier output to recover from a saturated state to a linear state. The output devices of the operational amplifier enter a saturation region when the output voltage exceeds the rated operating voltage, because of the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return to the linear state. After the charge carriers return to the linear state, the device begins to slew at the specified slew rate. Therefore, the propagation delay (in case of an overload condition) is the sum of the overload recovery time and the slew time. The overload recovery time for the LMV3xxA-Q1 family is approximately 850 ns.

7.4 Device Functional Modes

The LMV3xxA-Q1 family has a single functional mode. The devices are powered on as long as the power-supply voltage is between 2.5 V ($\pm 1.25\text{ V}$) and 5.5 V ($\pm 2.75\text{ V}$).

8 Application and Implementation

备注

以下应用部分中的信息不属于 TI 器件规格的范围，TI 不担保其准确性和完整性。TI 的客户应负责确定器件是否适用于其应用。客户应验证并测试其设计，以确保系统功能。

8.1 Application Information

The LMV3xxA-Q1 family of low-power, rail-to-rail output operational amplifiers is specifically designed for portable applications. The devices operate from 2.5 V to 5.5 V, are unity-gain stable, and are designed for for a wide range of general-purpose applications. The class AB output stage is capable of driving less than or equal to 10-k Ω loads connected to any point between V+ and V-. The input common-mode voltage range includes the negative rail, and allows the LMV3xxA-Q1 devices to be used in many single-supply applications.

8.2 Typical Application

8.2.1 LMV3xxA-Q1 Low-Side, Current Sensing Application

图 8-1 shows the LMV3xxA-Q1 configured in a low-side current sensing application.

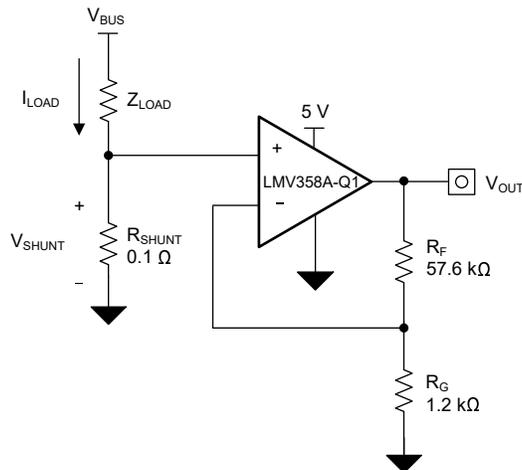


图 8-1. LMV3xxA-Q1 in a Low-Side, Current-Sensing Application

8.2.1.1 Design Requirements

The design requirements for this design are:

- Load current: 0 A to 1 A
- Output voltage: 4.9 V
- Maximum shunt voltage: 100 mV

8.2.1.2 Detailed Design Procedure

The transfer function of the circuit in [图 8-1](#) is given in [方程式 1](#).

$$V_{OUT} = I_{LOAD} \times R_{SHUNT} \times Gain \quad (1)$$

The load current (I_{LOAD}) produces a voltage drop across the shunt resistor (R_{SHUNT}). The load current is set from 0 A to 1 A. To keep the shunt voltage below 100 mV at maximum load current, the largest shunt resistor is shown using [方程式 2](#).

$$R_{SHUNT} = \frac{V_{SHUNT_MAX}}{I_{LOAD_MAX}} = \frac{100\text{ mV}}{1\text{ A}} = 100\text{ m}\Omega \quad (2)$$

Using [方程式 2](#), R_{SHUNT} is calculated to be 100 m Ω . The voltage drop produced by I_{LOAD} and R_{SHUNT} is amplified by the LMV3xxA-Q1 to produce an output voltage of approximately 0 V to 4.9 V. The gain needed by the LMV3xxA-Q1 to produce the necessary output voltage is calculated using [方程式 3](#).

$$Gain = \frac{(V_{OUT_MAX} - V_{OUT_MIN})}{(V_{IN_MAX} - V_{IN_MIN})} \quad (3)$$

Using [方程式 3](#), the required gain is calculated to be 49 V/V, which is set with resistors R_F and R_G . [方程式 4](#) sizes the resistors R_F and R_G , to set the gain of the LMV3xxA-Q1 to 49 V/V.

$$Gain = 1 + \frac{(R_F)}{(R_G)} \quad (4)$$

Selecting R_F as 57.6 k Ω and R_G as 1.2 k Ω provides a combination that equals 49 V/V. [图 8-2](#) shows the measured transfer function of the circuit shown in [图 8-1](#). Notice that the gain is only a function of the feedback and gain resistors. This gain is adjusted by varying the ratio of the resistors and the actual resistors values are determined by the impedance levels that the designer wants to establish. The impedance level determines the current drain, the effect that stray capacitance has, and a few other behaviors. There is no best impedance selection that works for every system, choose an impedance that is an excellent choice for the system parameters.

8.2.1.3 Application Curve

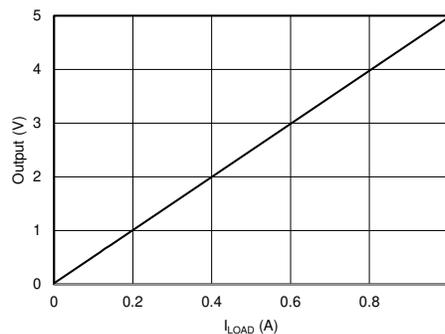


图 8-2. Low-Side, Current-Sense Transfer Function

8.2.2 Single-Supply Photodiode Amplifier

Photodiodes are used in many applications to convert light signals to electrical signals. The current through the photodiode is proportional to the photon energy absorbed, and is commonly in the range of a few hundred picoamps to a few tens of microamps. An amplifier in a transimpedance configuration is typically used to convert the low-level photodiode current to a voltage signal for processing in an MCU. The circuit shown in [图 8-3](#) is an example of a single-supply photodiode amplifier circuit using the LMV358A-Q1.

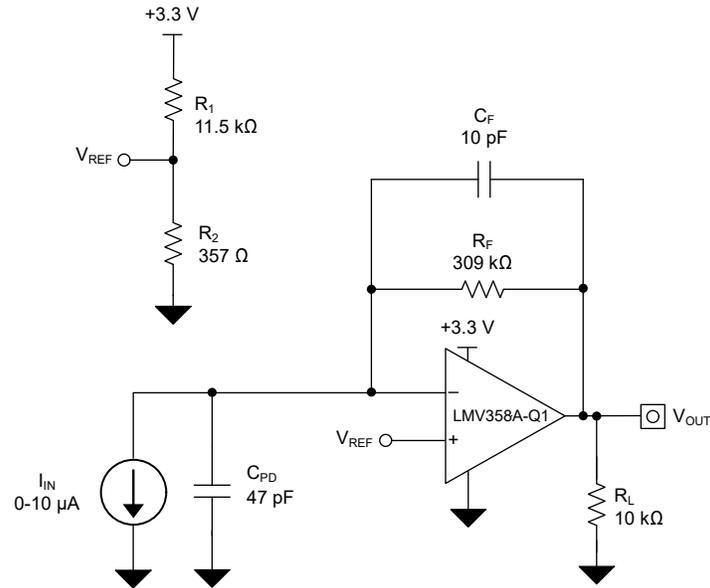


图 8-3. Single-Supply Photodiode Amplifier Circuit

8.2.2.1 Design Requirements

The design requirements for this design are:

- Supply voltage: 3.3 V
- Input: 0 μ A to 10 μ A
- Output: 0.1 V to 3.2 V
- Bandwidth: 50 kHz

8.2.2.2 Detailed Design Procedure

The transfer function between the output voltage (V_{OUT}), the input current, (I_{IN}) and the reference voltage (V_{REF}) is defined in [方程式 5](#).

$$V_{OUT} = I_{IN} \times R_F + V_{REF} \quad (5)$$

Where:

$$V_{REF} = V_+ \times \left(\frac{R_1 \times R_2}{R_1 + R_2} \right) \quad (6)$$

Set V_{REF} to 100 mV to meet the minimum output voltage level by setting R1 and R2 to meet the required ratio calculated in [方程式 7](#).

$$\frac{V_{REF}}{V_+} = \frac{0.1V}{3.3V} = 0.0303 \quad (7)$$

The closest resistor ratio to meet this ratio sets R1 to 11.5 k Ω and R2 to 357 Ω .

The required feedback resistance can be calculated based on the input current and desired output voltage.

$$R_F = \frac{V_{OUT} - V_{REF}}{I_{IN}} = \frac{3.2V - 0.1V}{10\mu A} = 310 \frac{kV}{A} \approx 309 k\Omega \quad (8)$$

Calculate the value for the feedback capacitor based on R_F and the desired -3-dB bandwidth, (f_{-3dB}) using [方程式 9](#).

$$C_F = \frac{1}{2 \times \pi \times R_F \times f_{-3dB}} = \frac{1}{2 \times \pi \times 309 k\Omega \times 50 kHz} = 10.3 pF \approx 10 pF \quad (9)$$

The minimum op amp bandwidth required for this application is based on the value of R_F , C_F , and the capacitance on the INx - pin of the LMV358A-Q1 which is equal to the sum of the photodiode shunt capacitance, (C_{PD}) the common-mode input capacitance, (C_{CM}) and the differential input capacitance (C_D) as [方程式 10](#) shows.

$$C_{IN} = C_{PD} + C_{CM} + C_D = 47 pF + 5 pF + 1 pF = 53 pF \quad (10)$$

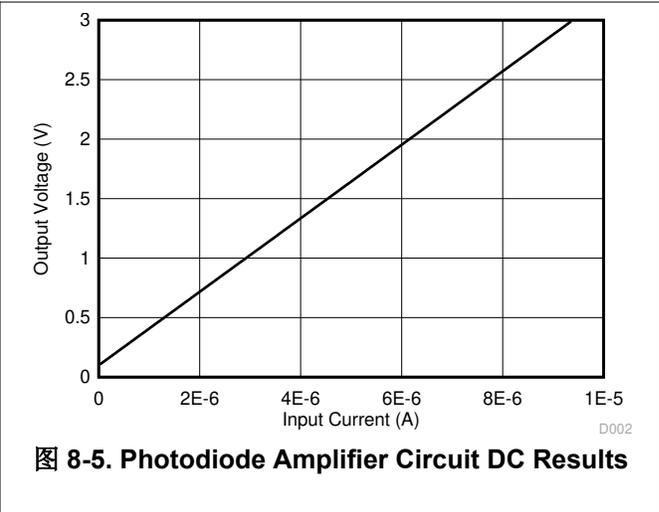
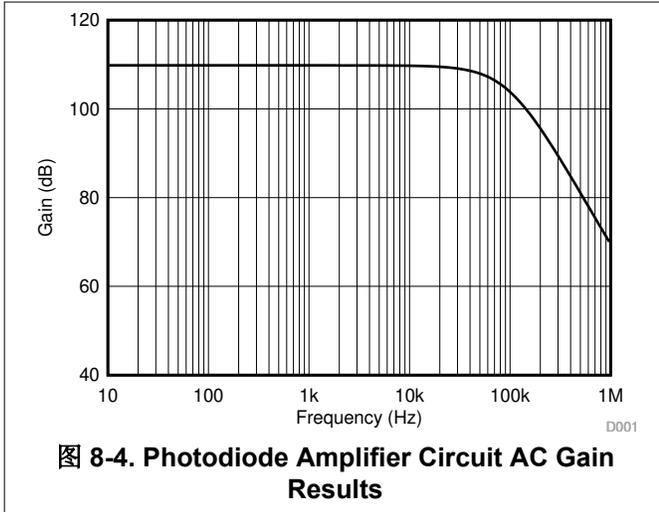
The minimum op amp bandwidth is calculated in [方程式 11](#).

$$F = BGW \geq \frac{C_{IN} + C_F}{2 \times \pi \times R_F \times C_F^2} \geq 324 kHz \quad (11)$$

The 1-MHz bandwidth of the LMV3xxA-Q1 meets the minimum bandwidth requirement and remains stable in this application configuration.

8.2.2.3 Application Curves

The measured current-to-voltage transfer function for the photodiode amplifier circuit is shown in [图 8-4](#). The measured performance of the photodiode amplifier circuit is shown in [图 8-5](#).



9 Power Supply Recommendations

The LMV3xxA-Q1 family is specified for operation from 2.5 V to 5.5 V (± 1.25 V to ± 2.75 V); many specifications apply from -40°C to 125°C . The *Typical Characteristics* section presents parameters that may exhibit significant variance with regard to operating voltage or temperature.

CAUTION

Supply voltages larger than 6 V may permanently damage the device; see the *Absolute Maximum Ratings* table.

Place 0.1- μF bypass capacitors close to the power-supply pins to reduce coupling errors from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see the *Layout Guidelines* section.

9.1 Input and ESD Protection

The LMV3xxA-Q1 family incorporates internal ESD protection circuits on all pins. For input and output pins, this protection primarily consists of current-steering diodes connected between the input and power-supply pins. These ESD protection diodes provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA. [Figure 9-1](#) shows how a series input resistor can be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and the value must be kept to a minimum in noise-sensitive applications.

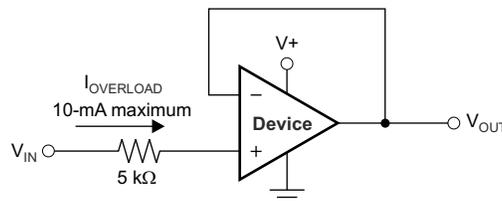


图 9-1. Input Current Protection

10 Layout

10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power connections of the board and propagate to the power pins of the op amp itself. Bypass capacitors are used to reduce the coupled noise by providing a low-impedance path to ground.
 - Connect low-ESR, 0.1- μ F ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is adequate for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Take care to physically separate digital and analog grounds, paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace at a 90 degree angle is much better as opposed to running the traces in parallel with the noisy trace.
- Place the external components as close to the device as possible, as shown in [Figure 10-2](#). Keeping R_F and R_G close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring may significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit can experience performance shifts resulting from moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low-temperature, post-cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

10.2 Layout Example

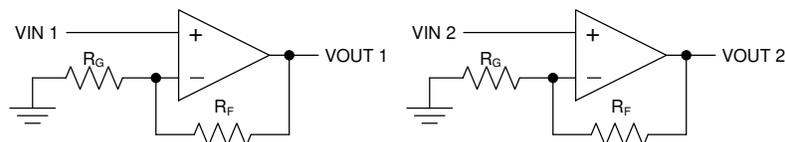


图 10-1. Schematic Representation for Figure 10-2

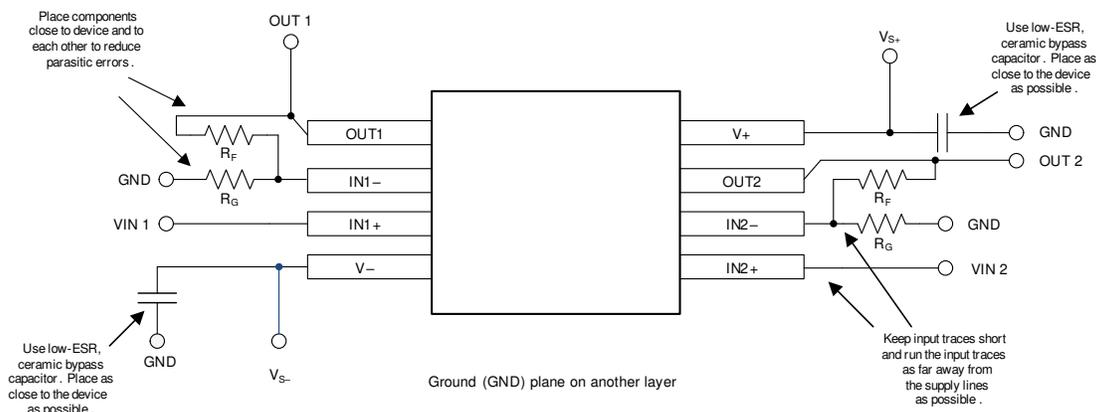


图 10-2. Layout Example

11 Device and Documentation Support

11.1 Documentation Support

11.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [EMI Rejection Ratio of Operational Amplifiers](#)

11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.3 支持资源

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.6 术语表

[TI 术语表](#) 本术语表列出并解释了术语、首字母缩略词和定义。

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most-current data available for the designated devices. This data is subject to change without notice and without revision of this document. For browser-based versions of this data sheet, see the left-hand navigation pane.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
LMV321AQDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	2S3F
LMV321AQDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	2S3F
LMV321AQDCKRQ1	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1N1
LMV321AQDCKRQ1.A	Active	Production	SC70 (DCK) 5	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	1N1
LMV321AUQDBVRQ1	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	2T7H
LMV321AUQDBVRQ1.A	Active	Production	SOT-23 (DBV) 5	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	2T7H
LMV324AQDRQ1	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LM324Q
LMV324AQDRQ1.A	Active	Production	SOIC (D) 14	2500 LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 125	LM324Q
LMV324AQDYRQ1	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM324Q
LMV324AQDYRQ1.A	Active	Production	SOT-23-THIN (DYY) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM324Q
LMV324AQPWRQ1	Active	Production	TSSOP (PW) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM324A
LMV324AQPWRQ1.A	Active	Production	TSSOP (PW) 14	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	LM324A
LMV358AQDGKRQ1	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	27FT
LMV358AQDGKRQ1.A	Active	Production	VSSOP (DGK) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	27FT
LMV358AQDRQ1	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	L358AQ
LMV358AQDRQ1.A	Active	Production	SOIC (D) 8	2500 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	L358AQ

(1) **Status:** For more details on status, see our [product life cycle](#).

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer:The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

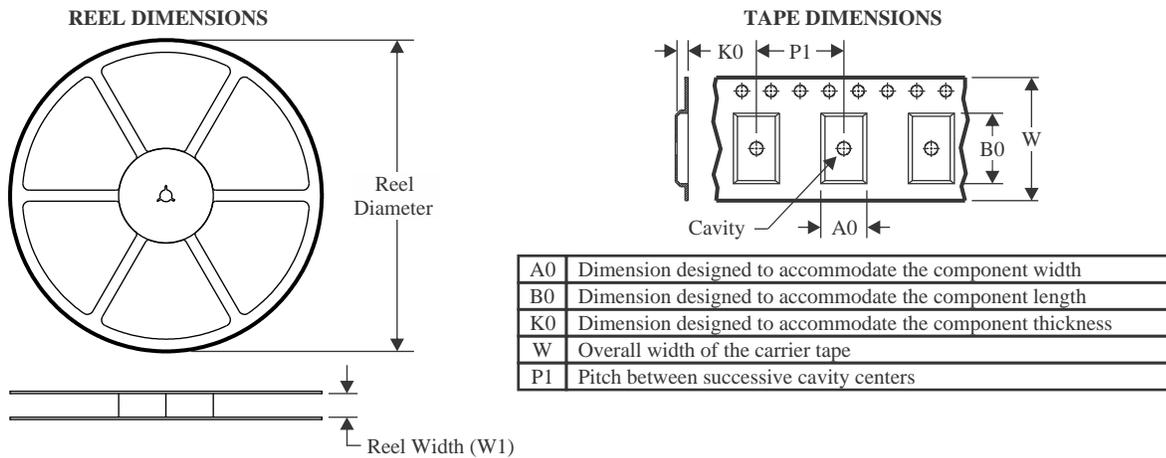
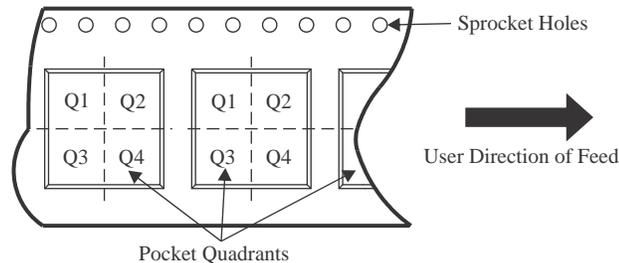
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF LMV321A-Q1, LMV324A-Q1, LMV358A-Q1 :

- Catalog : [LMV321A](#), [LMV324A](#), [LMV358A](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMV321AQDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321AQDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321AQDCKRQ1	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
LMV321AUQDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV321AUQDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
LMV324AQDRQ1	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
LMV324AQDYRQ1	SOT-23-THIN	DYY	14	3000	330.0	12.4	4.8	3.6	1.6	8.0	12.0	Q3
LMV324AQPWRQ1	TSSOP	PW	14	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
LMV358AQDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358AQDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.25	3.35	1.25	8.0	12.0	Q1
LMV358AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMV321AQDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
LMV321AQDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
LMV321AQDCKRQ1	SC70	DCK	5	3000	190.0	190.0	30.0
LMV321AUQDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
LMV321AUQDBVRQ1	SOT-23	DBV	5	3000	210.0	185.0	35.0
LMV324AQDRQ1	SOIC	D	14	2500	353.0	353.0	32.0
LMV324AQDYRQ1	SOT-23-THIN	DYY	14	3000	336.6	336.6	31.8
LMV324AQPWRQ1	TSSOP	PW	14	3000	353.0	353.0	32.0
LMV358AQDGKRQ1	VSSOP	DGK	8	2500	353.0	353.0	32.0
LMV358AQDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0
LMV358AQDRQ1	SOIC	D	8	2500	353.0	353.0	32.0

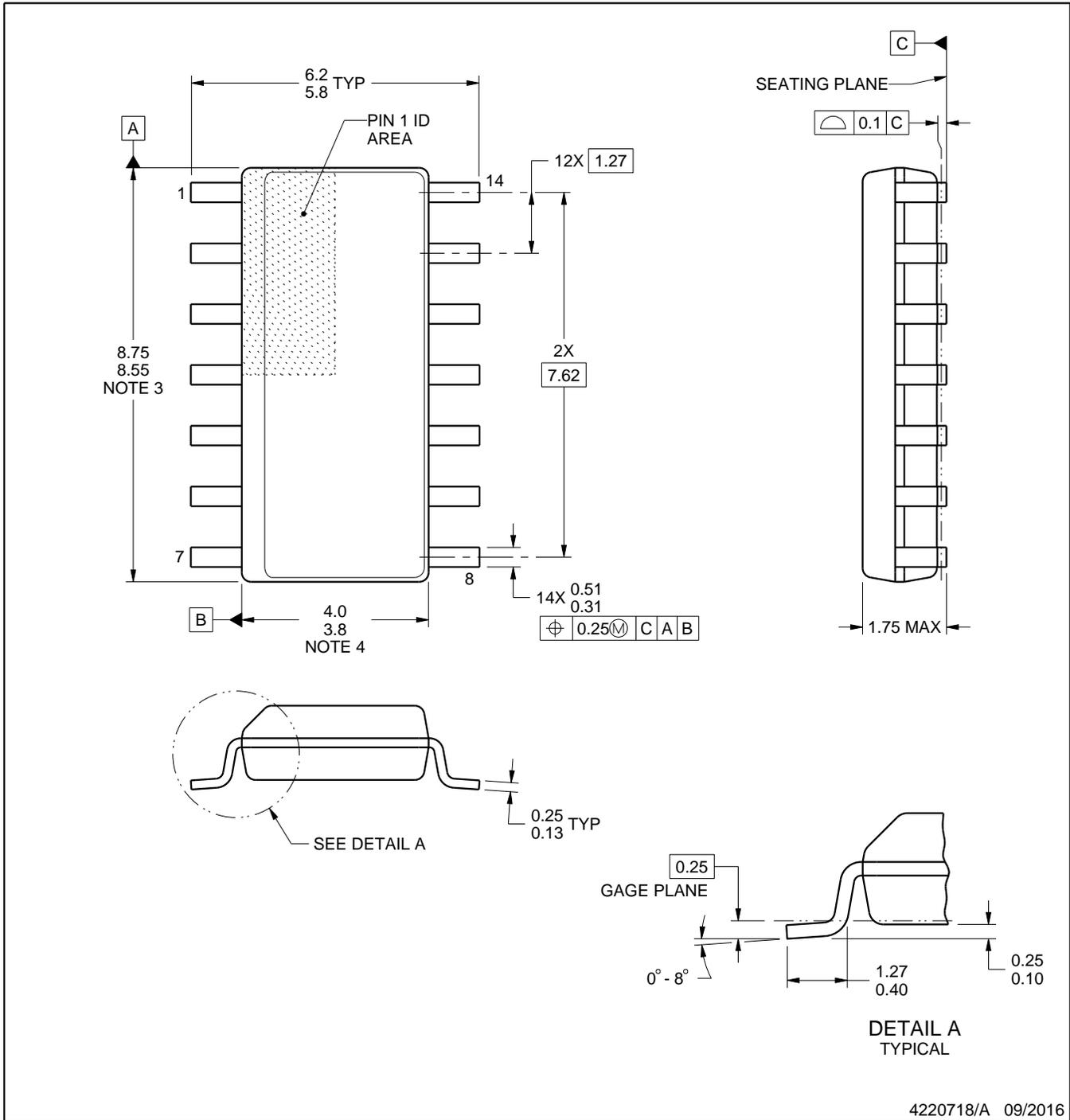
D0014A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

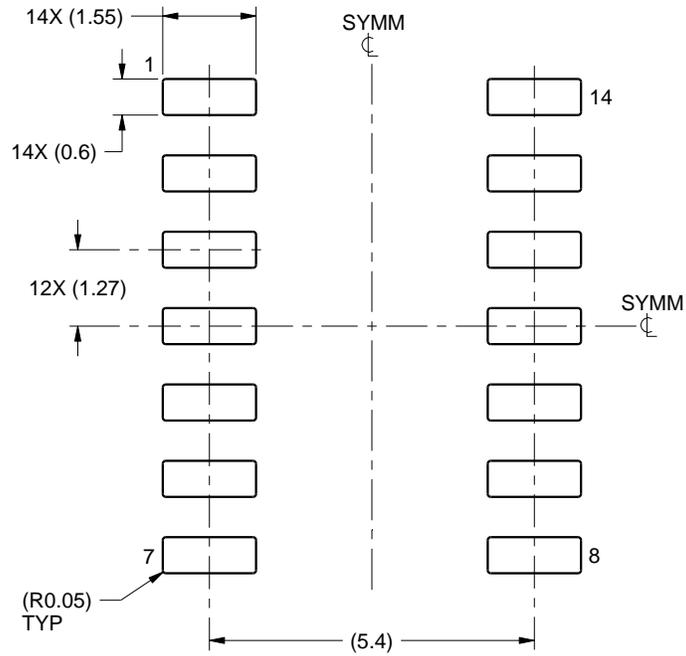
1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm, per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.43 mm, per side.
5. Reference JEDEC registration MS-012, variation AB.

EXAMPLE BOARD LAYOUT

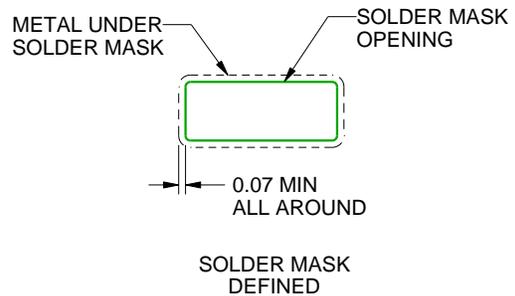
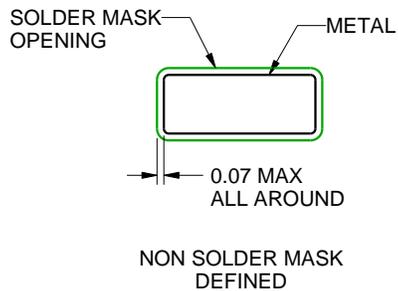
D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
SCALE:8X



SOLDER MASK DETAILS

4220718/A 09/2016

NOTES: (continued)

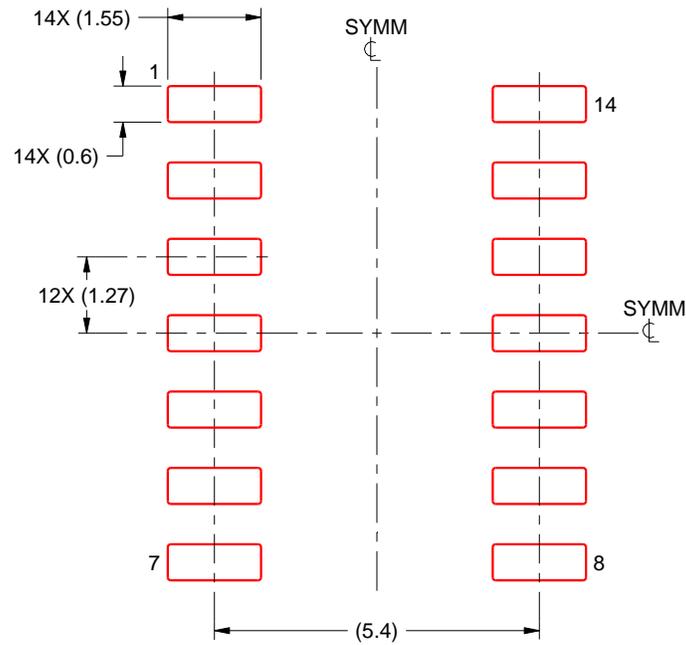
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0014A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:8X

4220718/A 09/2016

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

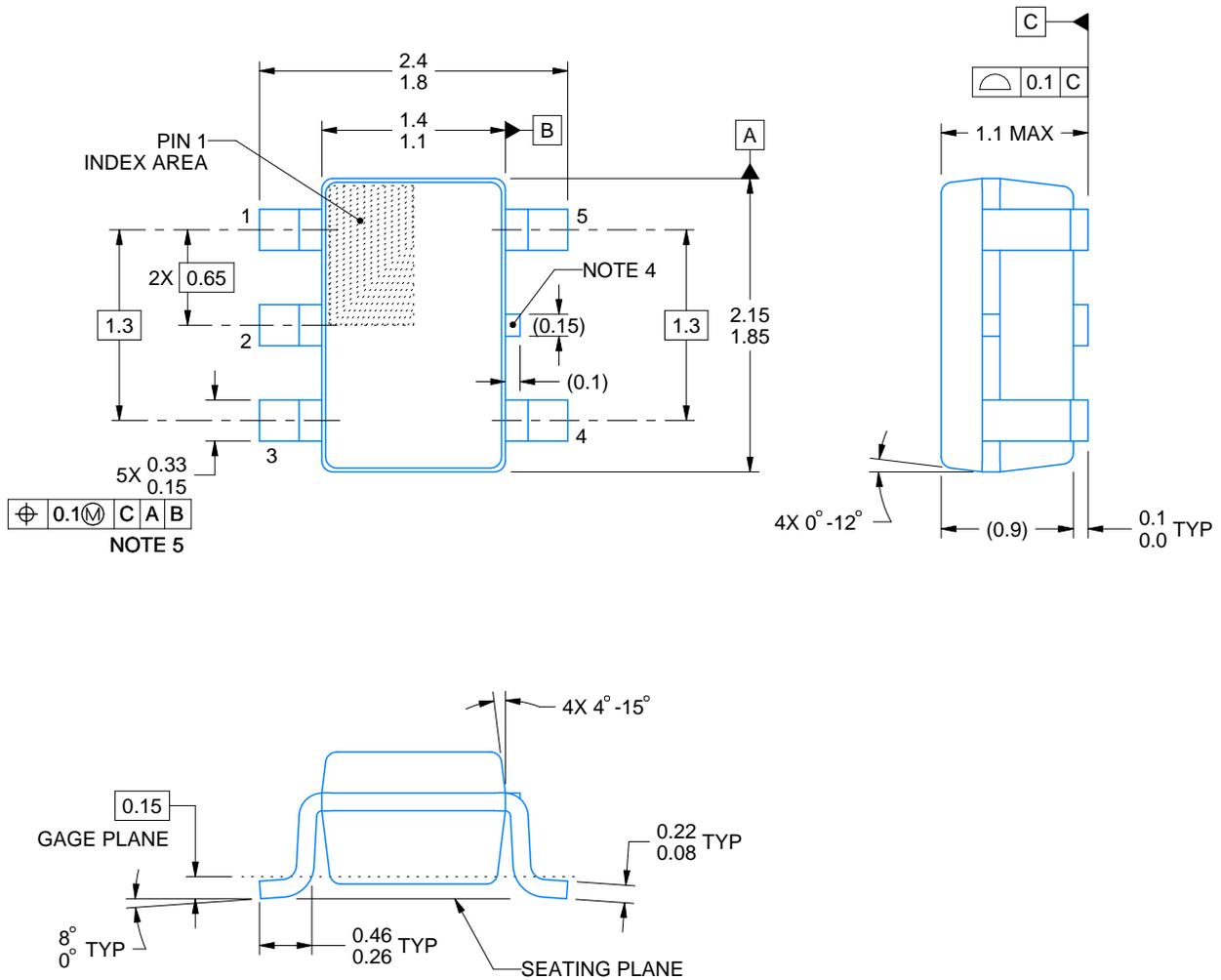
DCK0005A



PACKAGE OUTLINE

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



4214834/G 11/2024

NOTES:

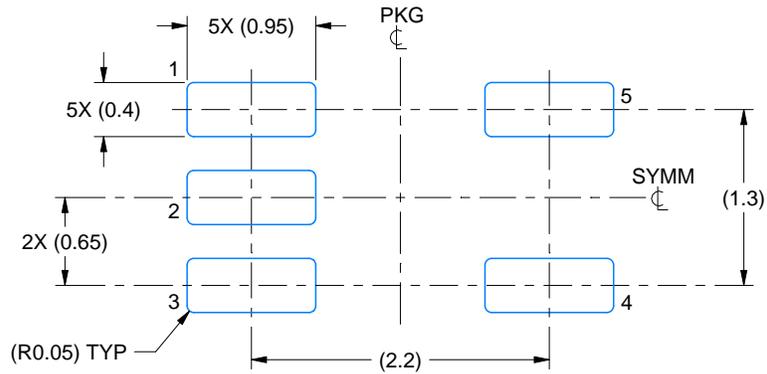
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

EXAMPLE BOARD LAYOUT

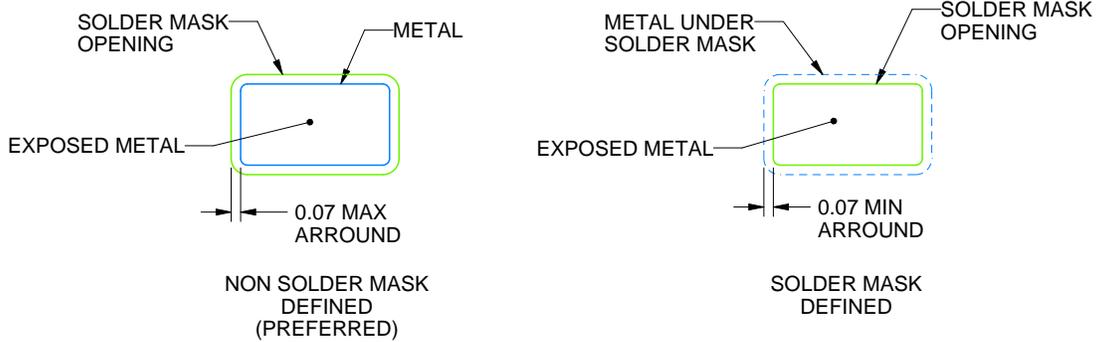
DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X



SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

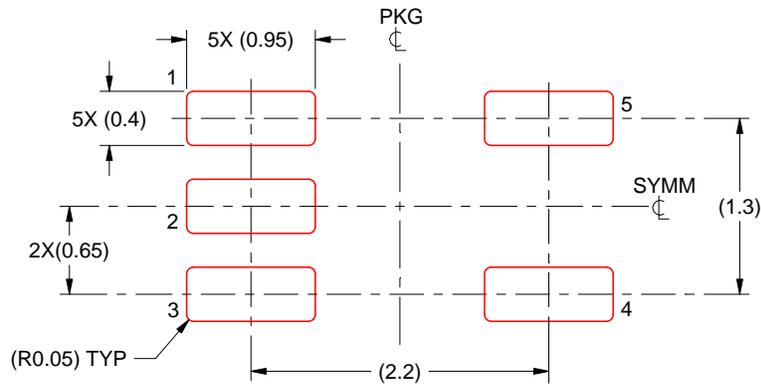
- 7. Publication IPC-7351 may have alternate designs.
- 8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE: 18X

4214834/G 11/2024

NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

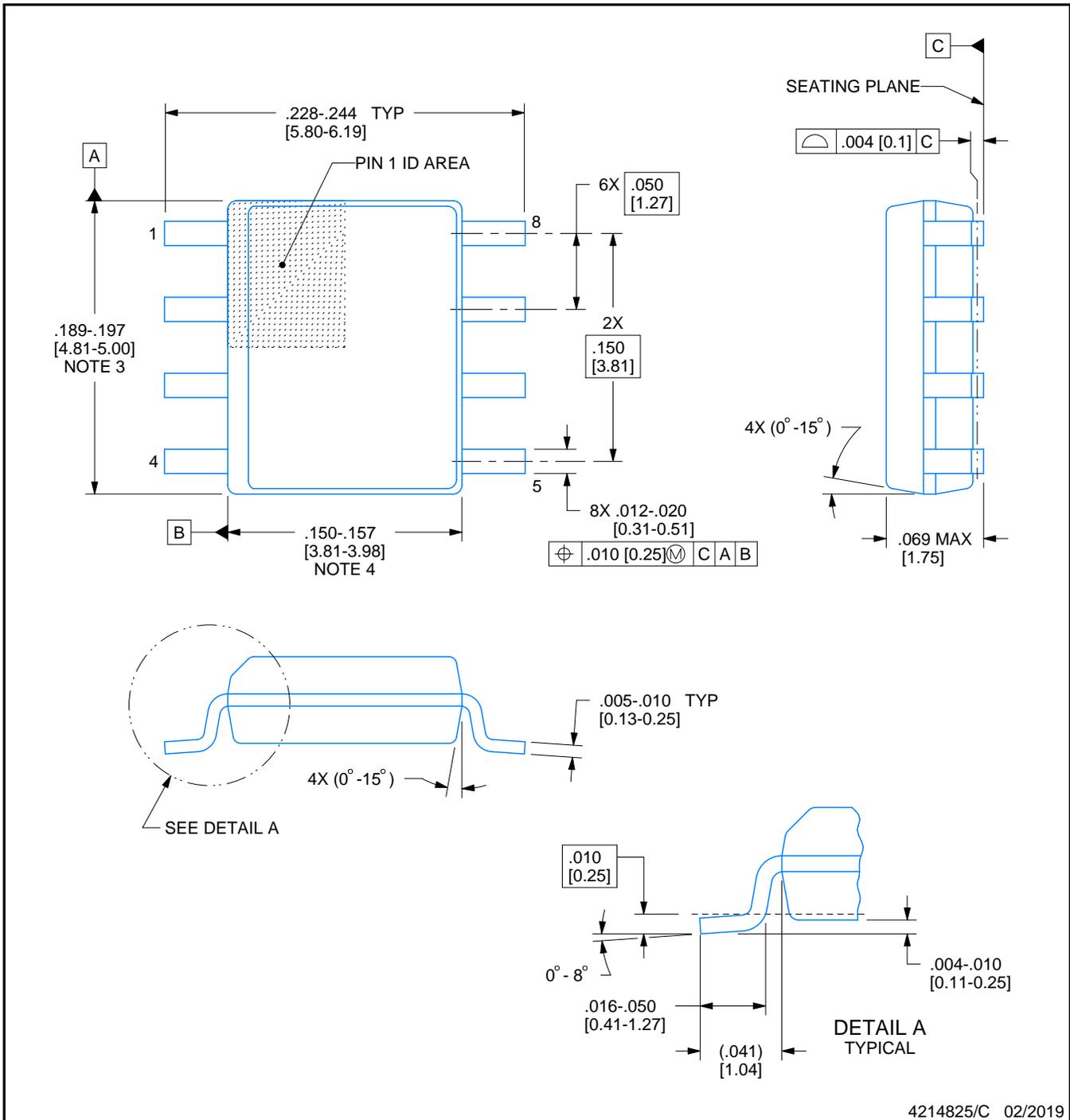


D0008A

PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



4214825/C 02/2019

NOTES:

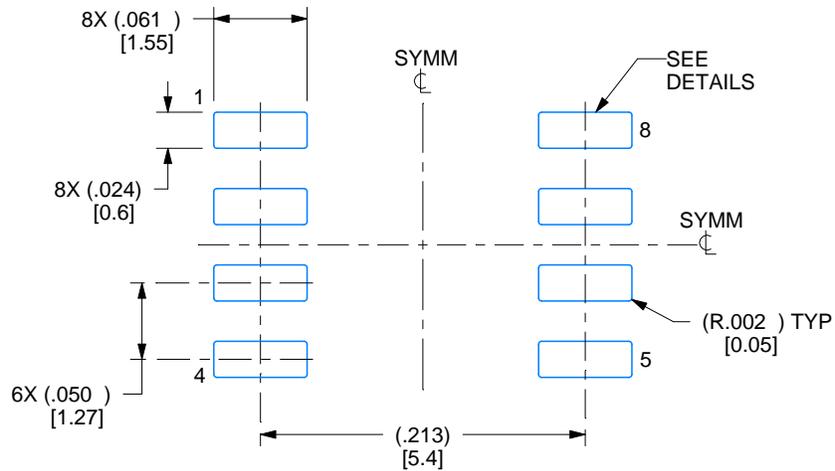
1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.

EXAMPLE BOARD LAYOUT

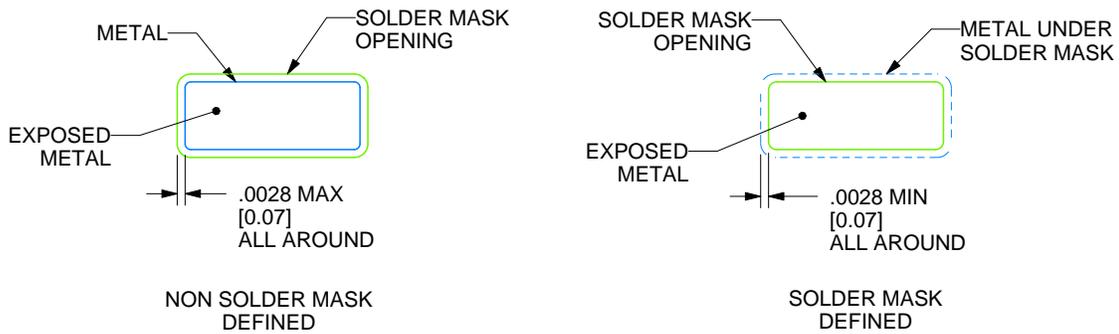
D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

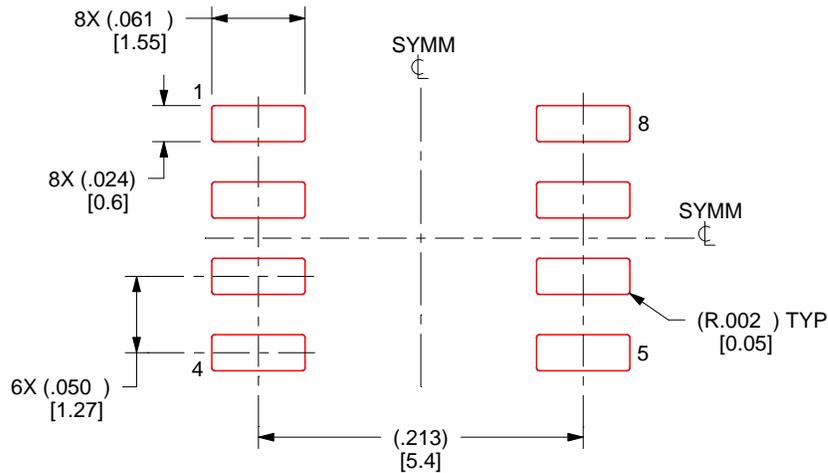
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

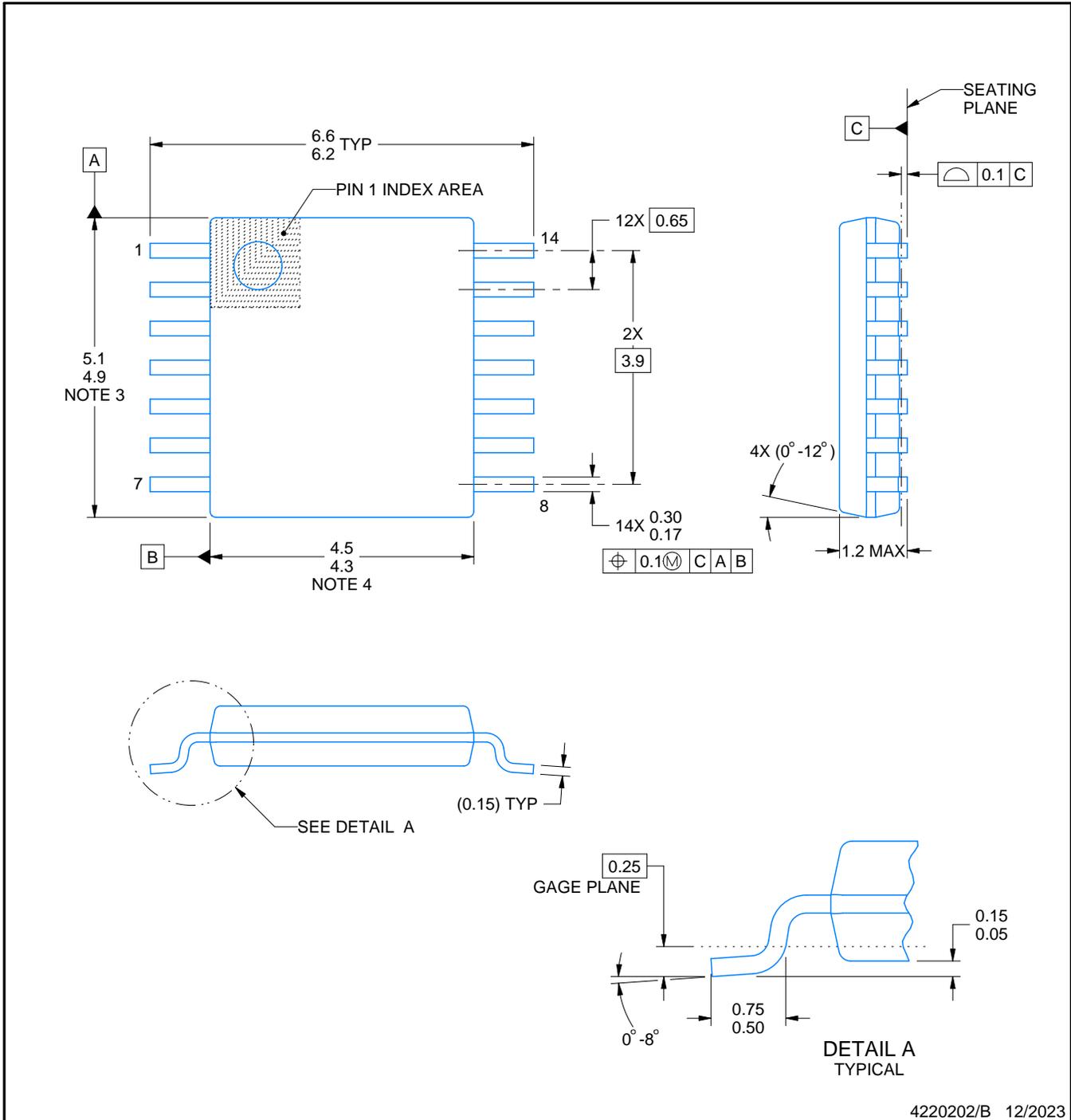


SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.



4220202/B 12/2023

NOTES:

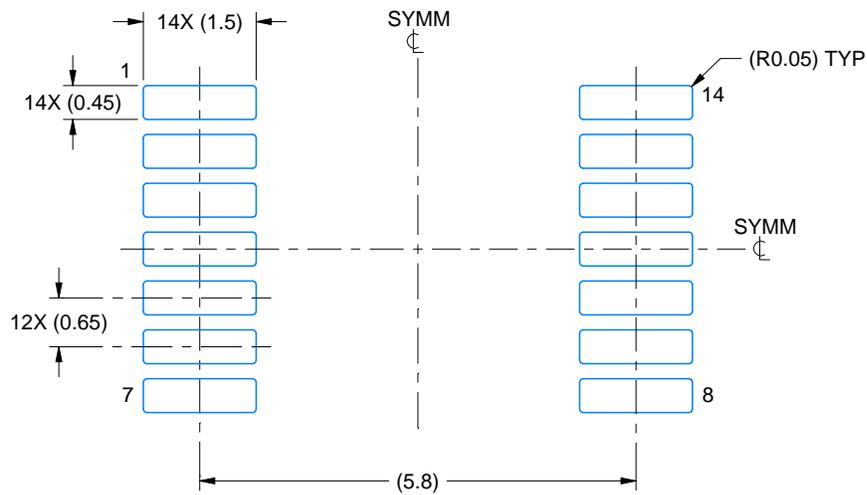
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.

EXAMPLE BOARD LAYOUT

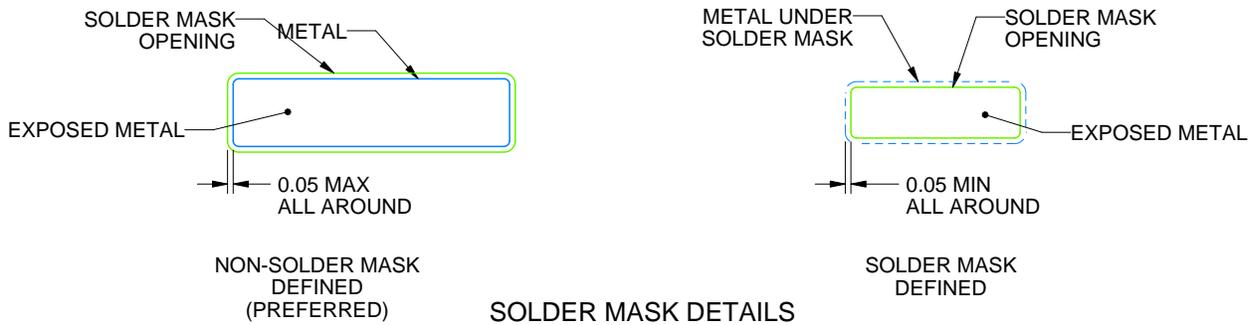
PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X



4220202/B 12/2023

NOTES: (continued)

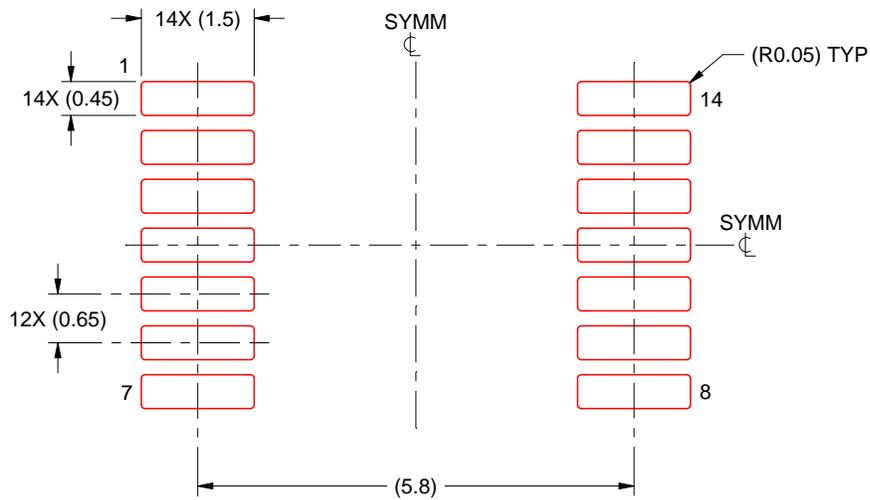
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

PW0014A

TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220202/B 12/2023

NOTES: (continued)

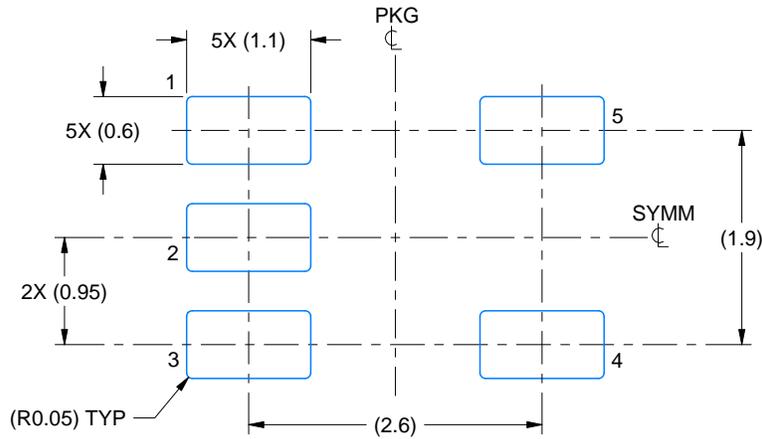
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

EXAMPLE BOARD LAYOUT

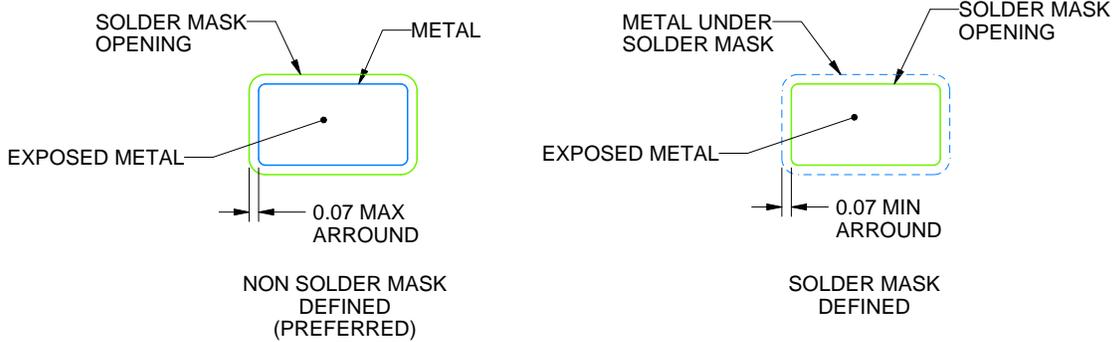
DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

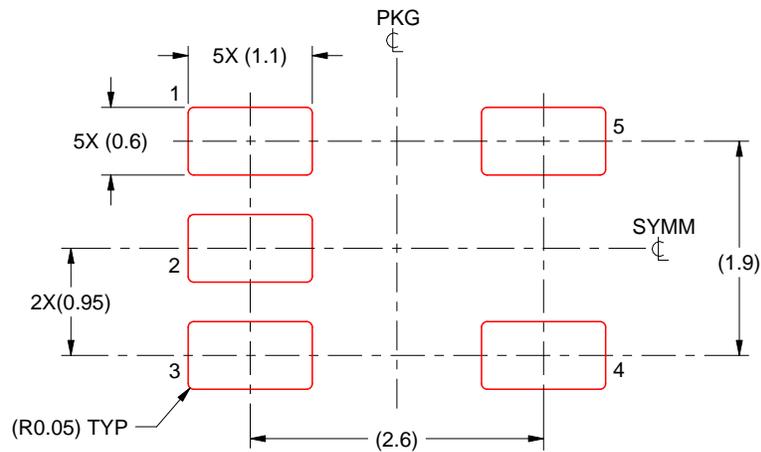
- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DBV0005A

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

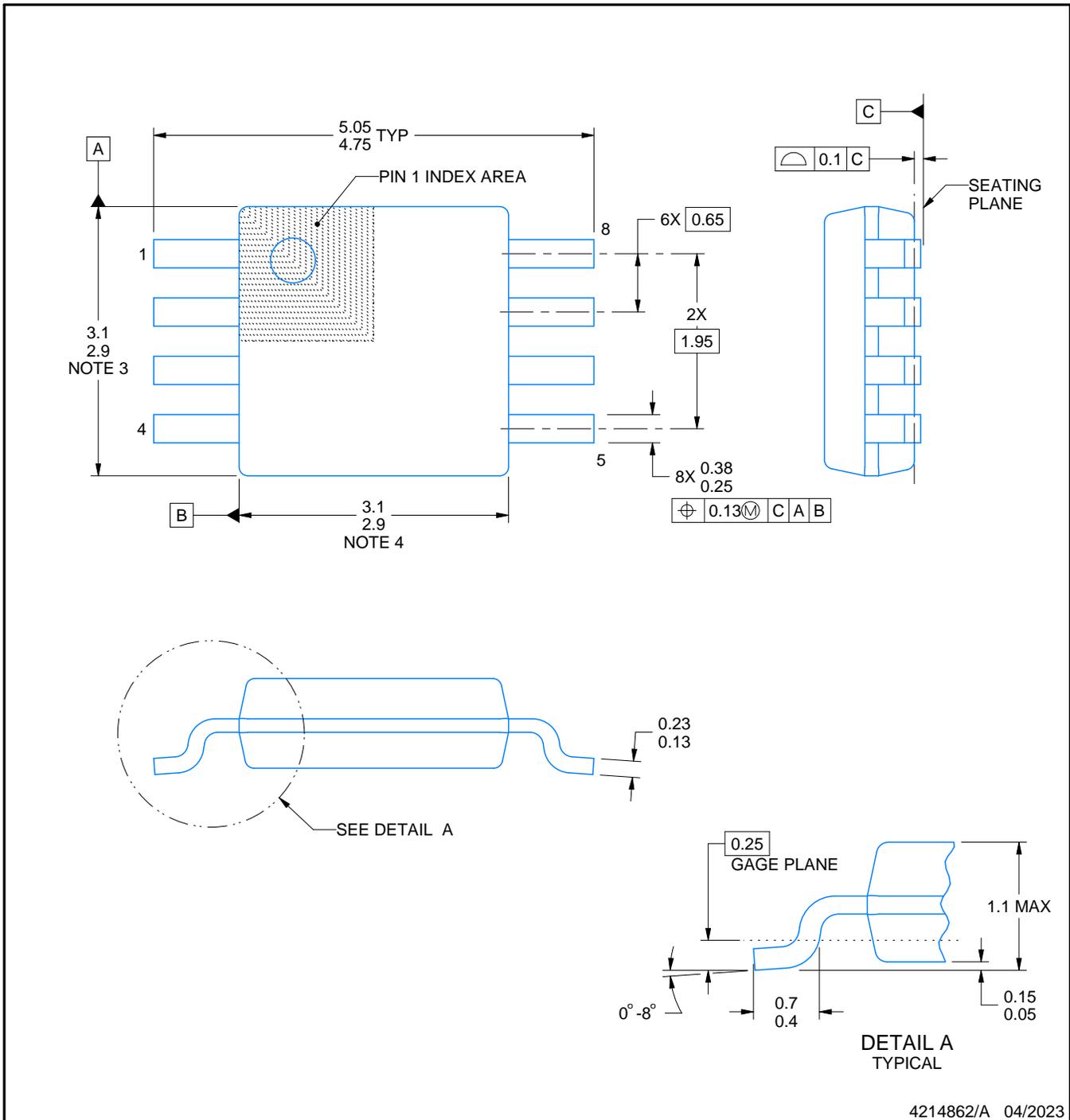
DGK0008A



PACKAGE OUTLINE

VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



4214862/A 04/2023

NOTES:

PowerPAD is a trademark of Texas Instruments.

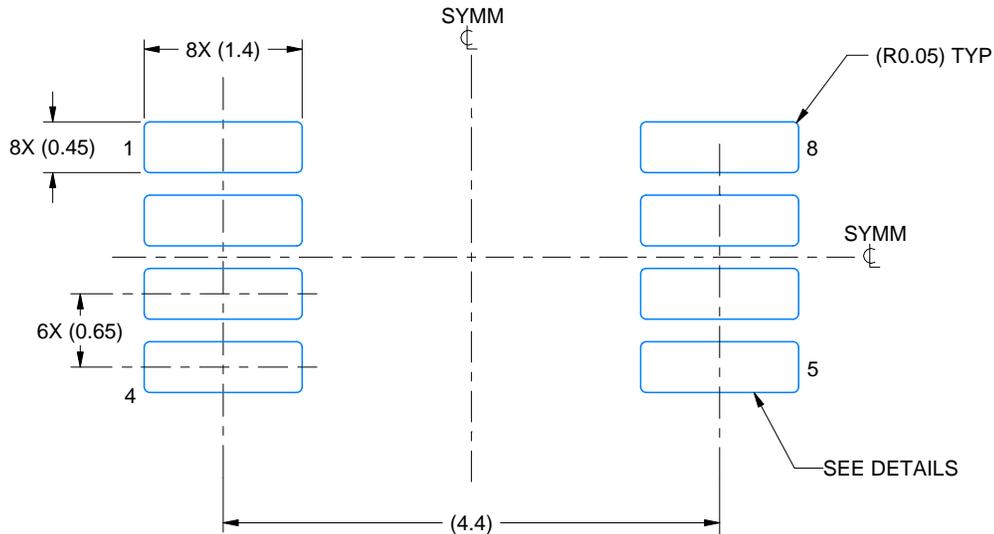
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.

EXAMPLE BOARD LAYOUT

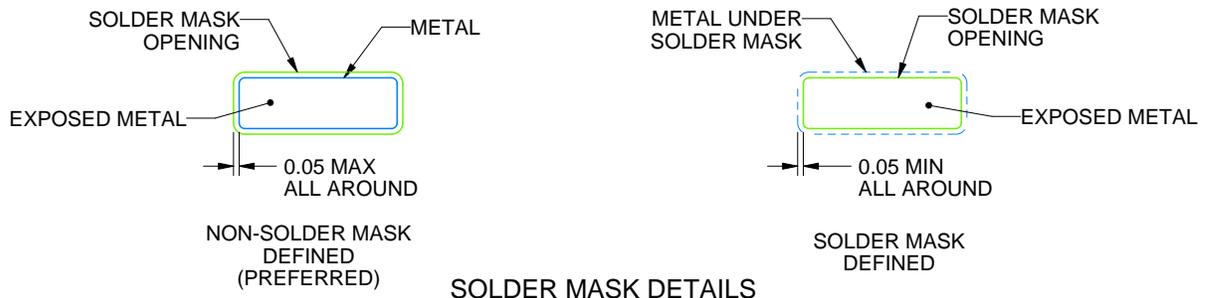
DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 15X



SOLDER MASK DETAILS

4214862/A 04/2023

NOTES: (continued)

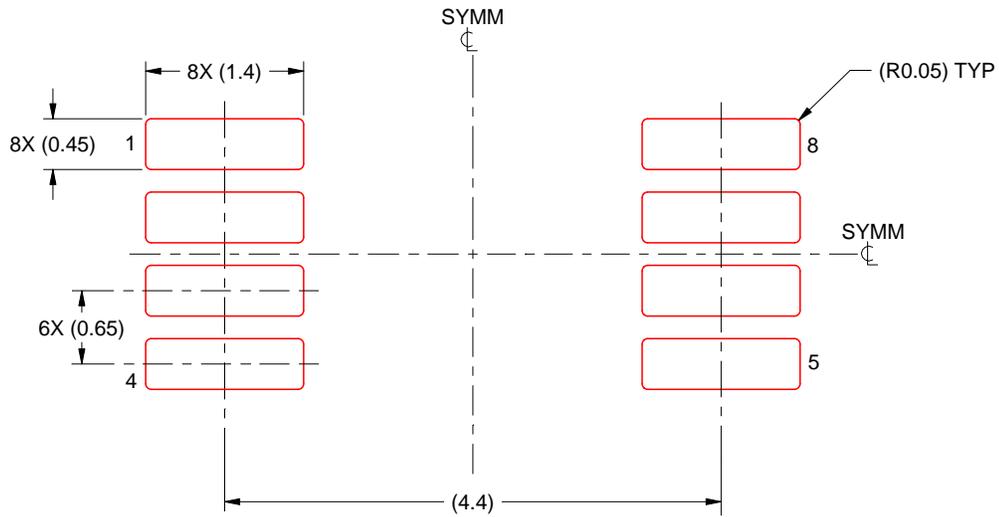
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.

EXAMPLE STENCIL DESIGN

DGK0008A

™ VSSOP - 1.1 mm max height

SMALL OUTLINE PACKAGE

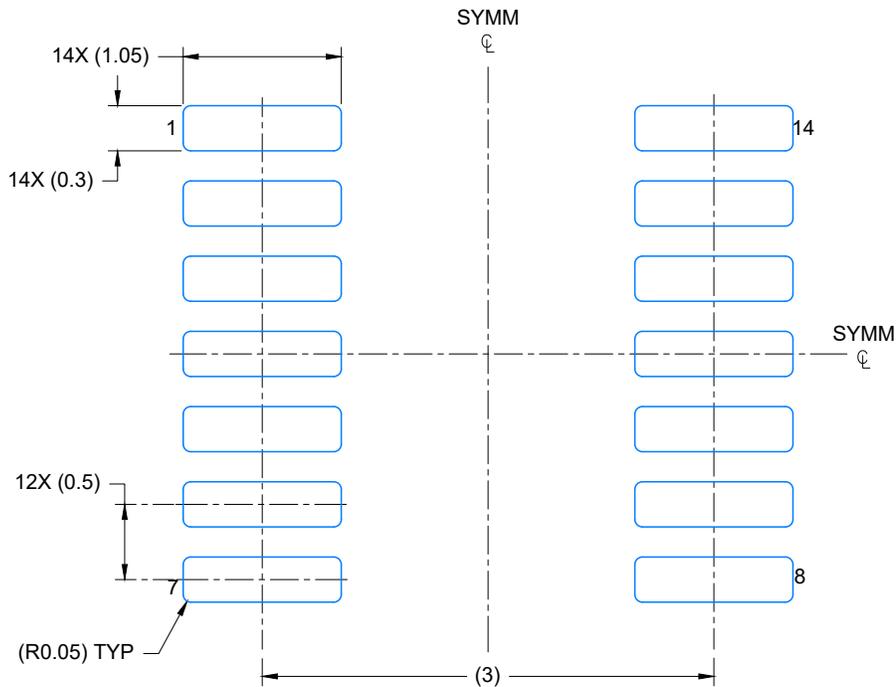


SOLDER PASTE EXAMPLE
SCALE: 15X

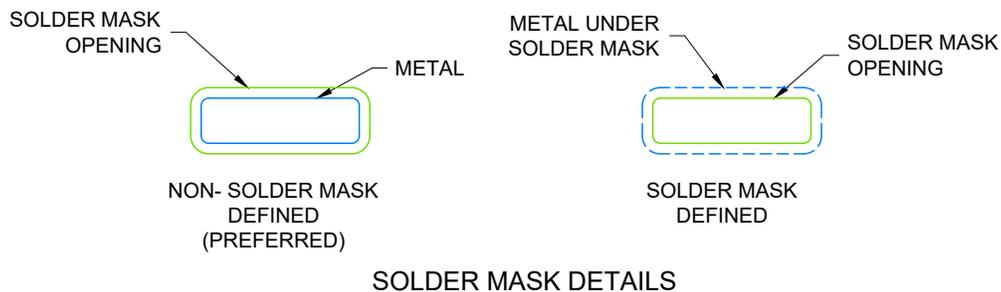
4214862/A 04/2023

NOTES: (continued)

11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.



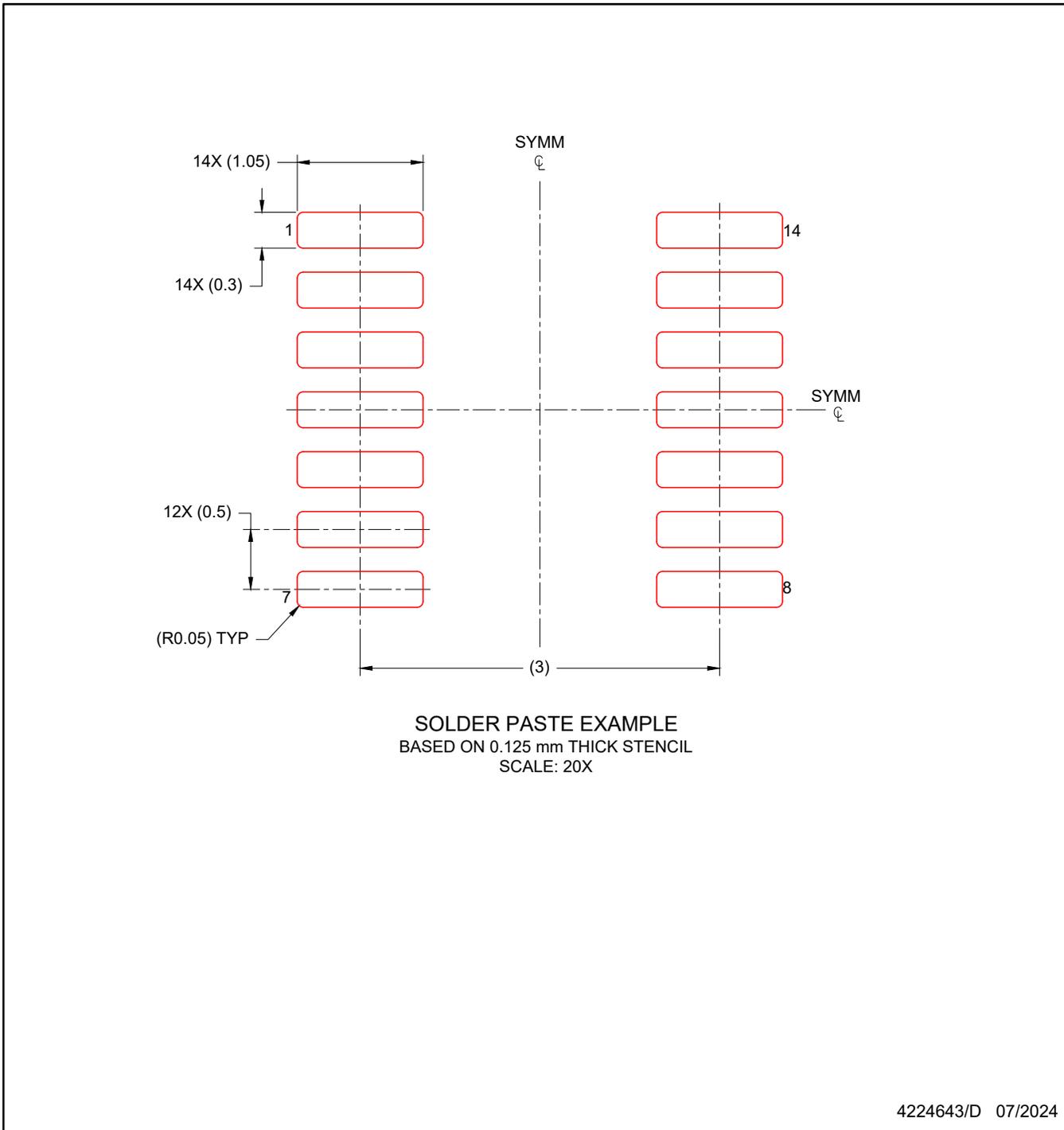
LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X



4224643/D 07/2024

NOTES: (continued)

- 6. Publication IPC-7351 may have alternate designs.
- 7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.

重要通知和免责声明

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